Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

DESCRIPTION

The MH16S72APHB is 16777216 - word by 72-bit Synchronous DRAM module. This consists of nine industry standard 16Mx8 Synchronous DRAMs in TSOP and one industory standard EEPROM in TSSOP.
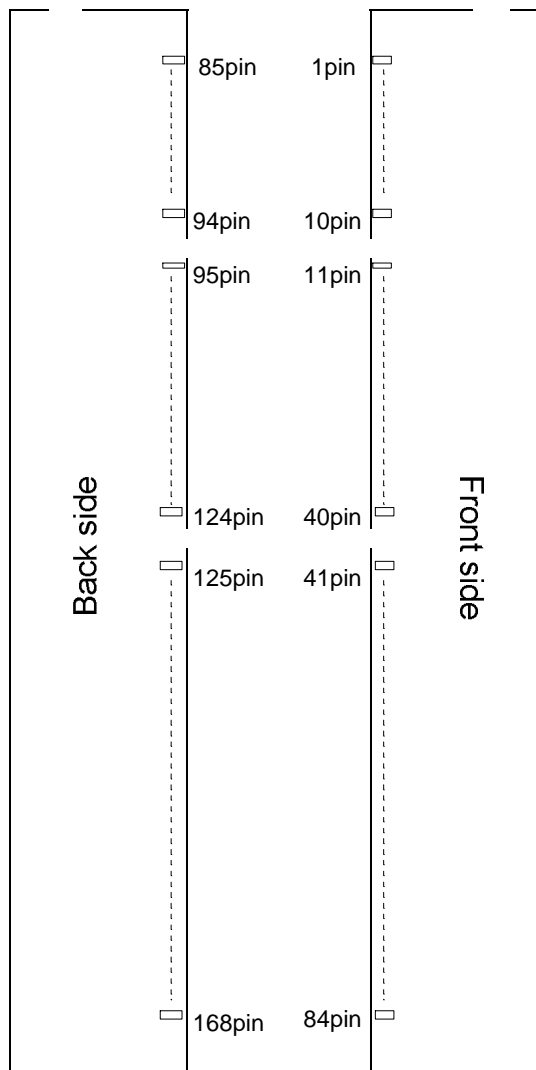
The mounting of TSOP on a card edge Dual Inline package provides any application where high densities and large quantities of memory are required.

This is a socket type - memory modules, suitable for easy interchange or addition of modules.

FEATURES

	Frequency	CLK Access Time (Component SDRAM)
-6	133MHz	5.4ns(CL=3)
-7	100MHz	6.0ns(CL=2)
-8	100MHz	6.0ns(CL=3)

- Utilizes industry standard 16M x 8 Synchronous DRAMs TSOP and industry standard EEPROM in TSSOP

- 168-pin (84-pin dual in-line package)

- single 3.3V±0.3V power supply

- Max. Clock frequency -6:133MHz,-7,8:100MHz

- Fully synchronous operation referenced to clock rising edge

- 4 bank operation controlled by BA0,1(Bank Address)

- /CAS latency- 2/3(programmable)

- Burst length- 1/2/4/8/Full Page(programmable)

- Burst type- sequential / interleave(programmable)

- Column access - random

- Auto precharge / All bank precharge controlled by A10

- Auto refresh and Self refresh

- 4096 refresh cycle /64ms

- LVTTL Interface

- Discrete IC and module design conform to PC100/PC133 specification.

Back side
85pin
94pin
95pin
124pin
125pin
168pin

Front side
1pin
10pin
11pin
40pin
41pin
84pin

APPLICATION

PC main memory

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

PIN NO.	PIN NAME	PIN NO.	PIN NAME	PIN NO.	PIN NAME	PIN NO.	PIN NAME
1	VSS	43	VSS	85	VSS	127	VSS
2	DQ0	44	NC	86	DQ32	128	CKE0
3	DQ1	45	/S2	87	DQ33	129	NC
4	DQ2	46	DQMB2	88	DQ34	130	DQMB6
5	DQ3	47	DQMB3	89	DQ35	131	DQMB7
6	VDD	48	NC	90	VDD	132	NC
7	DQ4	49	VDD	91	DQ36	133	VDD
8	DQ5	50	NC	92	DQ37	134	NC
9	DQ6	51	NC	93	DQ38	135	NC
10	DQ7	52	CB2	94	DQ39	136	CB6
11	DQ8	53	CB3	95	DQ40	137	CB7
12	VSS	54	VSS	96	VSS	138	VSS
13	DQ9	55	DQ16	97	DQ41	139	DQ48
14	DQ10	56	DQ17	98	DQ42	140	DQ49
15	DQ11	57	DQ18	99	DQ43	141	DQ50
16	DQ12	58	DQ19	100	DQ44	142	DQ51
17	DQ13	59	VDD	101	DQ45	143	VDD
18	VDD	60	DQ20	102	VDD	144	DQ52
19	DQ14	61	NC	103	DQ46	145	NC
20	DQ15	62	NC	104	DQ47	146	NC
21	CB0	63	NC	105	CB4	147	NC
22	CB1	64	VSS	106	CB5	148	VSS
23	VSS	65	DQ21	107	VSS	149	DQ53
24	NC	66	DQ22	108	NC	150	DQ54
25	NC	67	DQ23	109	NC	151	DQ55
26	VDD	68	VSS	110	VDD	152	VSS
27	/WE0	69	DQ24	111	/CAS	153	DQ56
28	DQMB0	70	DQ25	112	DQMB4	154	DQ57
29	DQMB1	71	DQ26	113	DQMB5	155	DQ58
30	/S0	72	DQ27	114	NC	156	DQ59
31	NC	73	VDD	115	/RAS	157	VDD
32	VSS	74	DQ28	116	VSS	158	DQ60
33	A0	75	DQ29	117	A1	159	DQ61
34	A2	76	DQ30	118	A3	160	DQ62
35	A4	77	DQ31	119	A5	161	DQ63
36	A6	78	VSS	120	A7	162	VSS
37	A8	79	CK2	121	A9	163	CK3
38	A10	80	NC	122	BA0	164	NC
39	BA1	81	WP	123	A11	165	SA0
40	VDD	82	SDA	124	VDD	166	SA1
41	VDD	83	SCL	125	CK1	167	SA2
42	CK0	84	VDD	126	NC	168	VDD

NC = No Connection

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Block Diagram
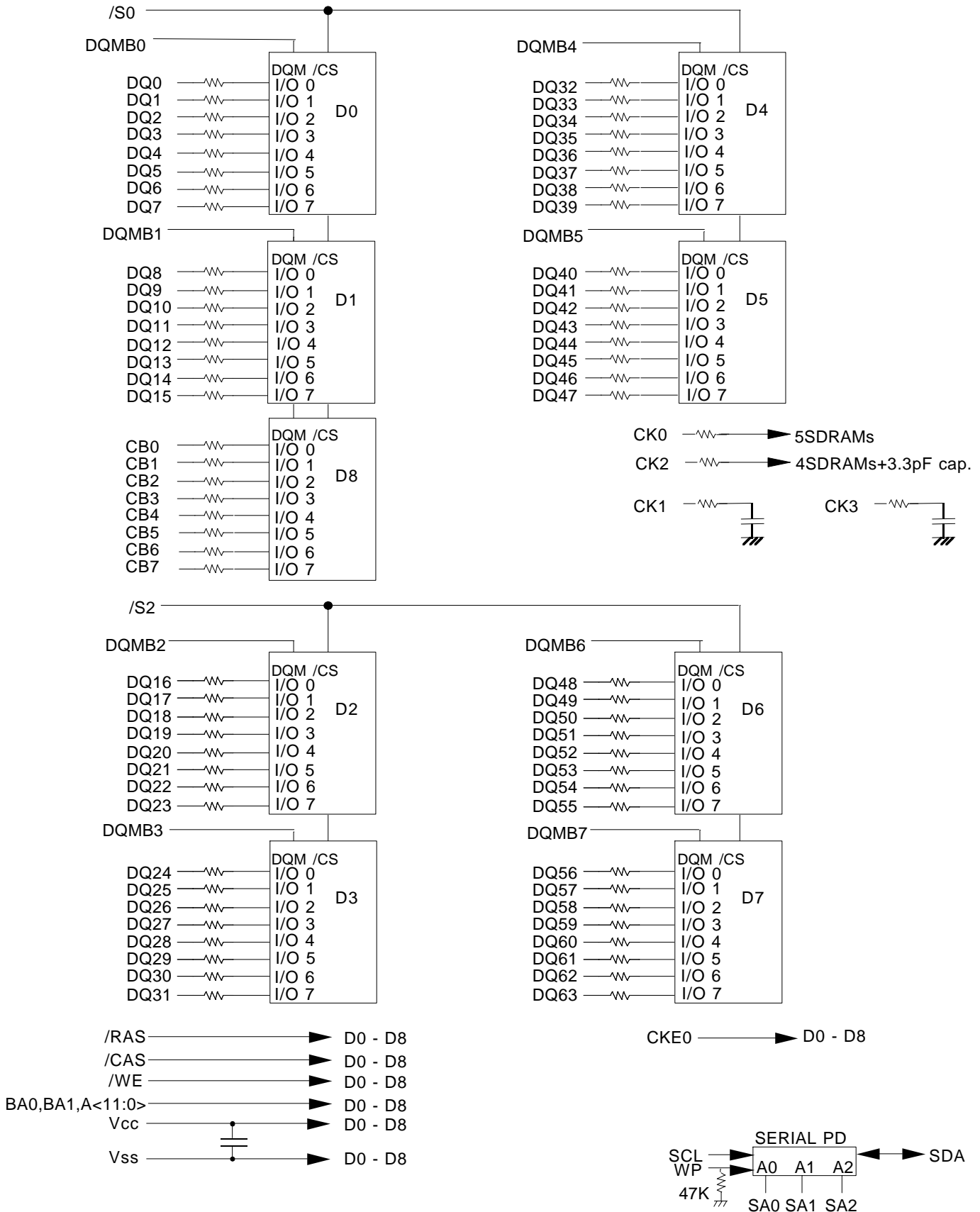
Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Serial Presence Detect Table I

Byte	Function described		SPD enrty data	SPD DATA(hex)
0	Defines # bytes written into serial memory at module mfgr		128	80
1	Total # bytes of SPD memory device		256 Bytes	08
2	Fundamental memory type		SDRAM	04
3	# Row Addresses on this assembly		A0-A11	0C
4	# Column Addresses on this assembly		A0-A9	0A
5	# Module Banks on this assembly		1BANK	01
6	Data Width of this assembly...		x72	48
7	... Data Width continuation		0	00
8	Voltage interface standard of this assembly		LVTTL	01
9	SDRAM Cycletime at Max. Supported CAS Latency (CL). Cycle time for CL=3	-6	7.5ns	75
		-7,-8	10ns	A0
10	SDRAM Access from Clock tAC for CL=3	-6	5.4ns	54
		-7,-8	6ns	60
11	DIMM Configuration type (Non-parity,Parity,ECC)		ECC	02
12	Refresh Rate/Type		self refresh(15.625uS)	80
13	SDRAM width,Primary DRAM		x8	08
14	Error Checking SDRAM data width		x8	08
15	Minimum Clock Delay,Back to Back Random Column Addresses		1	01
16	Burst Lengths Supported		1/2/4/8/Full page	8F
17	# Banks on Each SDRAM device		4bank	04
18	CAS# Latency		2/3	06
19	CS# Latency		0	01
20	Write Latency		0	01
21	SDRAM Module Attributes		non-buffered,non-registered	00
22	SDRAM Device Attributes:General		Precharge All,Auto precharge	0E
23	SDRAM Cycle time(2nd highest CAS latency) Cycle time for CL=2	-6	10ns	A0
		-7	10ns	A0
		-8	13ns	D0
24	SDRAM Access form Clock(2nd highest CAS latency) tAC for CL=2	-6	6ns	60
		-7	6ns	60
		-8	7ns	70
25	SDRAM Cycle time(3rd highest CAS latency)		N/A	00
26	SDRAM Access form Clock(3rd highest CAS latency)		N/A	00
27	Precharge to Active Minimum	-6	22.5ns	17
		-7,-8	20ns	14
28	Row Active to Row Active Min.	-6	15ns	0F
		-7,-8	20ns	14
29	RAS to CAS Delay Min	-6	22.5ns	17
		-7,-8	20ns	14
30	Active to Precharge Min	-6	45ns	2D
		-7,-8	50ns	32

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Serial Presence Detect Table II

31	Density of each bank on module		128MByte	20
32	Command and Address signal input setup time	-6	1.5ns	15
		-7,-8	2ns	20
33	Command and Address signal input hold time	-6	0.8ns	08
		-7,-8	1ns	10
34	Data signal input setup time	-6	1.5ns	15
		-7,-8	2ns	20
35	Data signal input hold time	-6	0.8ns	08
		-7,-8	1ns	10
36-61	Superset Information (may be used in future)		option	00
62	SPD Revision		rev 1.2B	12
63	Checksum for bytes 0-62		Check sum for -6	C7
			Check sum for -7	28
			Check sum for -8	68
64-71	Manufactures Jedec ID code per JEP-108E		MITSUBISHI	1CFFFFFFFFFFFFFF
72	Manufacturing location		Miyoshi,Japan	01
			Tajima,Japan	02
			NC,USA	03
			Germany	04
73-90	Manufactures Part Number		MH16S72APHB-6	4D48313653373241504842 2D362020202020
			MH16S72APHB-7	4D48313653373241504842 2D372020202020
			MH16S72APHB-8	4D48313653373241504842 2D382020202020
91-92	Revision Code		PCB revision	rrrr
93-94	Manufacturing date		year/week code	yyww
95-98	Assembly Serial Number		serial number	ssssssss
99-125	Manufacture Specific Data		option	00
126	Intetl specification frequency		100MHz	64
127	Intel specification CAS# Latency support	-6,-7	CL=2/3,AP,CK0,2	AF
		-8	CL=3,AP,CK0,2	AD
128+	Unused storage locations		open	00

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

PIN FUNCTION

CK (CK0 ~ CK3)	Input	Master Clock:All other inputs are referenced to the rising edge of CK
CKE0	Input	Clock Enable:CKE controls internal clock.When CKE is low,internal clock for the following cycle is ceased. CKE is also used to select auto / self refresh. After self refresh mode is started, CKE becomes asynchronous input.Self refresh is maintained as long as CKE is low.
/S (/S0,2)	Input	Chip Select: When /S is high,any command means No Operation.
/RAS,/CAS,/WE	Input	Combination of /RAS,/CAS,/WE defines basic commands.
A0-11	Input	A0-11 specify the Row/Column Address in conjunction with BA.The Row Address is specified by A0-11.The Column Address is specified by A0-9.A10 is also used to indicate precharge option.When A10 is high at a read / write command, an auto precharge is performed. When A10 is high at a precharge command, all banks are precharged.
BA0,1	Input	Bank Address:BA0,1 is not simply BA.BA specifies the bank to which a command is applied.BA0,1 must be set with ACT,PRE,READ,WRITE commands
DQ0-63 CB0-7	Input/Output	Data In and Data out are referenced to the rising edge of CK
DQMB0-7	Input	Din Mask/Output Disable:When DQMB is high in burst write.Din for the current cycle is masked.When DQMB is high in burst read,Dout is disabled at the next but one cycle.
Vdd,Vss	Power Supply	Power Supply for the memory mounted module.
SCL	Input	Serial clock for serial PD
SDA	Output	Serial data for serial PD
SA0-3	Input	Address input for serial PD

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

BASIC FUNCTIONS

The MH16S72APHB provides basic functions,bank(row)activate,burst read / write, bank(row)precharge,and auto / self refresh.

Each command is defined by control signals of /RAS,/CAS and /WE at CK rising edge. In addition to 3 signals,/S,CKE and A10 are used as chip select,refresh option,and precharge option,respectively.

To know the detailed definition of commands please see the command truth table.
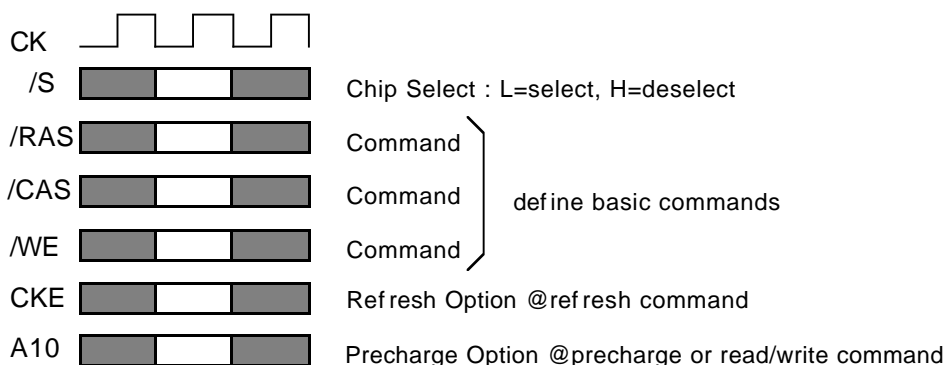
Activate(ACT) [/RAS =L, /CAS = /WE =H]

ACT command activates a row in an idle bank indicated by BA.

Read(READ) [/RAS =H,/CAS =L, /WE =H]

READ command starts burst read from the active bank indicated by BA.First output data appears after /CAS latency. When A10 =H at this command,the bank is deactivated after the burst read(auto-precharge,**READA**).

Write(WRITE) [/RAS =H, /CAS = /WE =L]

WRITE command starts burst write to the active bank indicated by BA. Total data length to be written is set by burst length. When A10 =H at this command, the bank is deactivated after the burst write(auto-precharge,**WRITEA**).

Precharge(PRE) [/RAS =L, /CAS =H,/WE =L]

PRE command deactivates the active bank indicated by BA. This command also terminates burst read / write operation. When A10 =H at this command, both banks are deactivated(precharge all, **PREA**).

Auto-Refresh(REFA) [/RAS =/CAS =L, /WE =CKE =H]

REFA command starts auto-refresh cycle. Refresh address including bank address are generated internally. After this command, the banks are precharged automatically.

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

COMMAND TRUTH TABLE

COMMAND	MNEMONIC	CKE n-1	CKE n	/S	/RAS	/CAS	/WE	BA0,1	A11	A10	A0-9
Deselect	DESEL	H	X	H	X	X	X	X	X	X	X
No Operation	NOP	H	X	L	H	H	H	X	X	X	X
Row Adress Entry & Bank Activate	ACT	H	X	L	L	H	H	V	V	V	V
Single Bank Precharge	PRE	H	X	L	L	H	L	V	X	L	X
Precharge All Bank	PREA	H	X	L	L	H	L	X	X	H	X
Column Address Entry & Write	WRITE	H	X	L	H	L	L	V	V	L	V
Column Address Entry & Write with Auto-Precharge	WRITEA	H	X	L	H	L	L	V	V	H	V
Column Address Entry & Read	READ	H	X	L	H	L	H	V	V	L	V
Column Address Entry & Read with Auto Precharge	READA	H	X	L	H	L	H	V	V	H	V
Auto-Refresh	REFA	H	H	L	L	L	H	X	X	X	X
Self-Refresh Entry	REFS	H	L	L	L	L	H	X	X	X	X
Self-Refresh Exit	REFSX	L	H	H	X	X	X	X	X	X	X
		L	H	L	H	H	H	X	X	X	X
Burst Terminate	TERM	H	X	L	H	H	L	X	X	X	X
Mode Register Set	MRS	H	X	L	L	L	L	L	L	L	V*1

H =High Level, L = Low Level, V = Valid, X = Don't Care, n = CK cycle number

NOTE:
1.A7-9 = 0, A0-6 = Mode Address

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

FUNCTION TRUTH TABLE

Current State	/S	/RAS	/CAS	/WE	Address	Command	Action
IDLE	H	X	X	X	X	DESEL	NOP
	L	H	H	H	X	NOP	NOP
	L	H	H	L	BA	TBST	ILLEGAL*2
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL*2
	L	L	H	H	BA,RA	ACT	Bank Active,Latch RA
	L	L	H	L	BA,A10	PRE/PREA	NOP*4
	L	L	L	H	X	REFA	Auto-Refresh*5
	L	L	L	L	Op-Code, Mode-Add	MRS	Mode Register Set*5
ROW ACTIVE	H	X	X	X	X	DESEL	NOP
	L	H	H	H	X	NOP	NOP
	L	H	H	L	BA	TBST	NOP
	L	H	L	H	BA,CA,A10	READ/READA	Begin Read,Latch CA, Determine Auto-Precharge
	L	H	L	L	BA,CA,A10	WRITE/ WRITEA	Begin Write,Latch CA, Determine Auto-Precharge
	L	L	H	H	BA,RA	ACT	Bank Active/ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	Precharge/Precharge All
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
READ	H	X	X	X	X	DESEL	NOP(Continue Burst to END)
	L	H	H	H	X	NOP	NOP(Continue Burst to END)
	L	H	H	L	BA	TBST	Terminate Burst
	L	H	L	H	BA,CA,A10	READ/READA	Terminate Burst,Latch CA, Begin New Read,Determine Auto-Precharge*3
	L	H	L	L	BA,CA,A10	WRITE/WRITEA	Terminate Burst,Latch CA, Begin Write,Determine Auto-Precharge*3
	L	L	H	H	BA,RA	ACT	Bank Active/ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	Terminate Burst,Precharge
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

FUNCTION TRUTH TABLE(continued)

Current State	/S	/RAS	/CAS	/WE	Address	Command	Action
WRITE	H	X	X	X	X	DESEL	NOP(Continue Burst to END)
	L	H	H	H	X	NOP	NOP(Continue Burst to END)
	L	H	H	L	BA	TBST	Terminate Burst
	L	H	L	H	BA,CA,A10	READ/READA	Terminate Burst,Latch CA, Begin Read,Determine Auto-Precharge*3
	L	H	L	L	BA,CA,A10	WRITE/ WRITEA	Terminate Burst,Latch CA, Begin Write,Determine Auto-Precharge*3
	L	L	H	H	BA,RA	ACT	Bank Active/ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	Terminate Burst,Precharge
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
READ with AUTO PRECHARGE	H	X	X	X	X	DESEL	NOP(Continue Burst to END)
	L	H	H	H	X	NOP	NOP(Continue Burst to END)
	L	H	H	L	BA	TBST	ILLEGAL
	L	H	L	H	BA,CA,A10	READ/READA	ILLEGAL
	L	H	L	L	BA,CA,A10	WRITE/ WRITEA	ILLEGAL
	L	L	H	H	BA,RA	ACT	Bank Active/ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL*2
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
WRITE with AUTO PRECHARGE	H	X	X	X	X	DESEL	NOP(Continue Burst to END)
	L	H	H	H	X	NOP	NOP(Continue Burst to END)
	L	H	H	L	BA	TBST	ILLEGAL
	L	H	L	H	BA,CA,A10	READ/READA	ILLEGAL
	L	H	L	L	BA,CA,A10	WRITE/ WRITEA	ILLEGAL
	L	L	H	H	BA,RA	ACT	Bank Active/ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL*2
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

FUNCTION TRUTH TABLE(continued)

Current State	/S	/RAS	/CAS	/WE	Address	Command	Action
PRE - CHARGING	H	X	X	X	X	DESEL	NOP(Idle after tRP)
	L	H	H	H	X	NOP	NOP(Idle after tRP)
	L	H	H	L	BA	TBST	ILLEGAL*2
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL*2
	L	L	H	H	BA,RA	ACT	ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	NOP*4(Idle after tRP)
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
ROW ACTIVATING	H	X	X	X	X	DESEL	NOP(Row Active after tRCD
	L	H	H	H	X	NOP	NOP(Row Active after tRCD
	L	H	H	L	BA	TBST	ILLEGAL*2
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL*2
	L	L	H	H	BA,RA	ACT	ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL*2
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
WRITE RE-COVERING	H	X	X	X	X	DESEL	NOP
	L	H	H	H	X	NOP	NOP
	L	H	H	L	BA	TBST	ILLEGAL*2
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL*2
	L	L	H	H	BA,RA	ACT	ILLEGAL*2
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL*2
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

FUNCTION TRUTH TABLE(continued)

Current State	/S	/RAS	/CAS	/WE	Address	Command	Action
RE-FRESHING	H	X	X	X	X	DESEL	NOP(Idle after tRC)
	L	H	H	H	X	NOP	NOP(Idle after tRC)
	L	H	H	L	BA	TBST	ILLEGAL
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL
	L	L	H	H	BA,RA	ACT	ILLEGAL
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL
MODE REGISTER SETTING	H	X	X	X	X	DESEL	NOP(Idle after tRSC)
	L	H	H	H	X	NOP	NOP(Idle after tRSC)
	L	H	H	L	BA	TBST	ILLEGAL
	L	H	L	X	BA,CA,A10	READ/WRITE	ILLEGAL
	L	L	H	H	BA,RA	ACT	ILLEGAL
	L	L	H	L	BA,A10	PRE/PREA	ILLEGAL
	L	L	L	H	X	REFA	ILLEGAL
	L	L	L	L	Op-Code, Mode-Add	MRS	ILLEGAL

ABBREVIATIONS:
H = Hige Level, L = Low Level, X = Don't Care
BA = Bank Address, RA = Row Address, CA = Column Address, NOP = No Operation

NOTES:
1. All entries assume that CKE was High during the preceding clock cycle and the current clock cycle.
2. ILLEGAL to bank in specified state; function may be legal in the bank indicated by BA, depending on the state of that bank.
3. Must satisfy bus contention, bus turn around, write recovery requirements.
4. NOP to bank precharging or in idle state. May precharge bank indicated by BA.
5. ILLEGAL if any bank is not idle.

ILLEGAL = Device operation and / or date-integrity are not guaranteed.

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

FUNCTION TRUTH TABLE FOR CKE

Current State	CKE n-1	CKE n	/S	/RAS	/CAS	/WE	Add	Action
SELF - REFRESH*1	H	X	X	X	X	X	X	INVALID
	L	H	H	X	X	X	X	Exit Self-Refresh(Idle after tRC)
	L	H	L	H	H	H	X	Exit Self-Refresh(Idle after tRC)
	L	H	L	H	H	L	X	ILLEGAL
	L	H	L	H	L	X	X	ILLEGAL
	L	H	L	L	X	X	X	ILLEGAL
	L	L	X	X	X	X	X	NOP(Maintain Self-Refresh)
POWER DOWN	H	X	X	X	X	X	X	INVALID
	L	H	X	X	X	X	X	Exit Power Down to Idle
	L	L	X	X	X	X	X	NOP(Maintain Self-Refresh)
ALL BANKS IDLE*2	H	H	X	X	X	X	X	Refer to Function Truth Table
	H	L	L	L	L	H	X	Enter Self-Refresh
	H	L	H	X	X	X	X	Enter Power Down
	H	L	L	H	H	H	X	Enter Power Down
	H	L	L	H	H	L	X	ILLEGAL
	H	L	L	H	L	X	X	ILLEGAL
	H	L	L	L	X	X	X	ILLEGAL
	L	X	X	X	X	X	X	Refer to Current State = Power Down
ANY STATE other than listed above	H	H	X	X	X	X	X	Refer to Function Truth Table
	H	L	X	X	X	X	X	Begin CK0 Suspend at Next Cycle*3
	L	H	X	X	X	X	X	Exit CK0 Suspend at Next Cycle*3
	L	L	X	X	X	X	X	Maintain CK0 Suspend

ABBREVIATIONS:
H = High Level, L = Low Level, X = Don't Care

NOTES:
1. CKE Low to High transition will re-enable CK and other inputs **asynchronously**.
   A minimum setup time must be satisfied before any command other than EXIT.
2. Power-Down and Self-Refresh can be entered only from the All banks idle State.
3. Must be legal command.

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

SIMPLIFIED STATE DIAGRAM

SELF REFRESH

REFS

REFSX

MODE REGISTER SET

MRS

IDLE

REFA

AUTO REFRESH

CKEL

CKEH

POWER DOWN

CLK SUSPEND

ACT

CKEL

CKEH

TBST(for Full Page)

ROW ACTIVE

TBST(for Full Page)

WRITE

WRITEA

READA

READ

CKEL

WRITE SUSPEND

WRITE

READ

READ

WRITE

READ

READ SUSPEND

CKEL

CKEH

CKEH

WRITEA

READA

WRITEA

READA

CKEL

WRITEA SUSPEND

WRITEA

PRE

READA

READA SUSPEND

CKEL

CKEH

CKEH

PRE

PRE

POWER APPLIED

POWER ON

PRE

PRE CHARGE

Automatic Sequence

Command Sequence

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

POWER ON SEQUENCE

Before starting normal operation, the following power on sequence is necessary to prevent a SDRAM from damaged or malfunctioning.

1. Apply power and start clock. Attempt to maintain CKE high, DQMB0-7 high and NOP condition at the inputs.
2. Maintain stable power, stable clock, and NOP input conditions for a minimum of 200us.
3. Issue precharge commands for all banks. (PRE or PREA)
4. After all banks become idle state (after tRP), issue 8 or more auto-refresh commands.
5. Issue a mode register set command to initialize the mode register.

After these sequence, the SDRAM is idle state and ready for normal operation.

MODE REGISTER

Burst Length, Burst Type and /CAS Latency can be programmed by setting the mode register(MRS). The mode register stores these date until the next MRS command, which may be issue when both banks are in idle state. After tRSC from a MRS command, the SDRAM is ready for new command.

BA0	BA1	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0
0	0	0	0	WM	0	0	LTMODE			BT	BL		

CK
/S
/RAS
/CAS
/WE
BA0,1 A11-0   V

CL	/CAS LATENCY
0 0 0	R
0 0 1	R
0 1 0	2
0 1 1	3
1 0 0	R
1 0 1	R
1 1 0	R
1 1 1	R

LATENCY MODE

BL	BT= 0	BT= 1
0 0 0	1	1
0 0 1	2	2
0 1 0	4	4
0 1 1	8	8
1 0 0	R	R
1 0 1	R	R
1 1 0	R	R
1 1 1	FP	R

BURST LENGTH

BURST TYPE	0	SEQUENTIAL
	1	INTERLEAVED

WRITE MODE	0	BURST
	1	SINGLE BIT

R:Reserved for Future Use
FP: Full Page

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
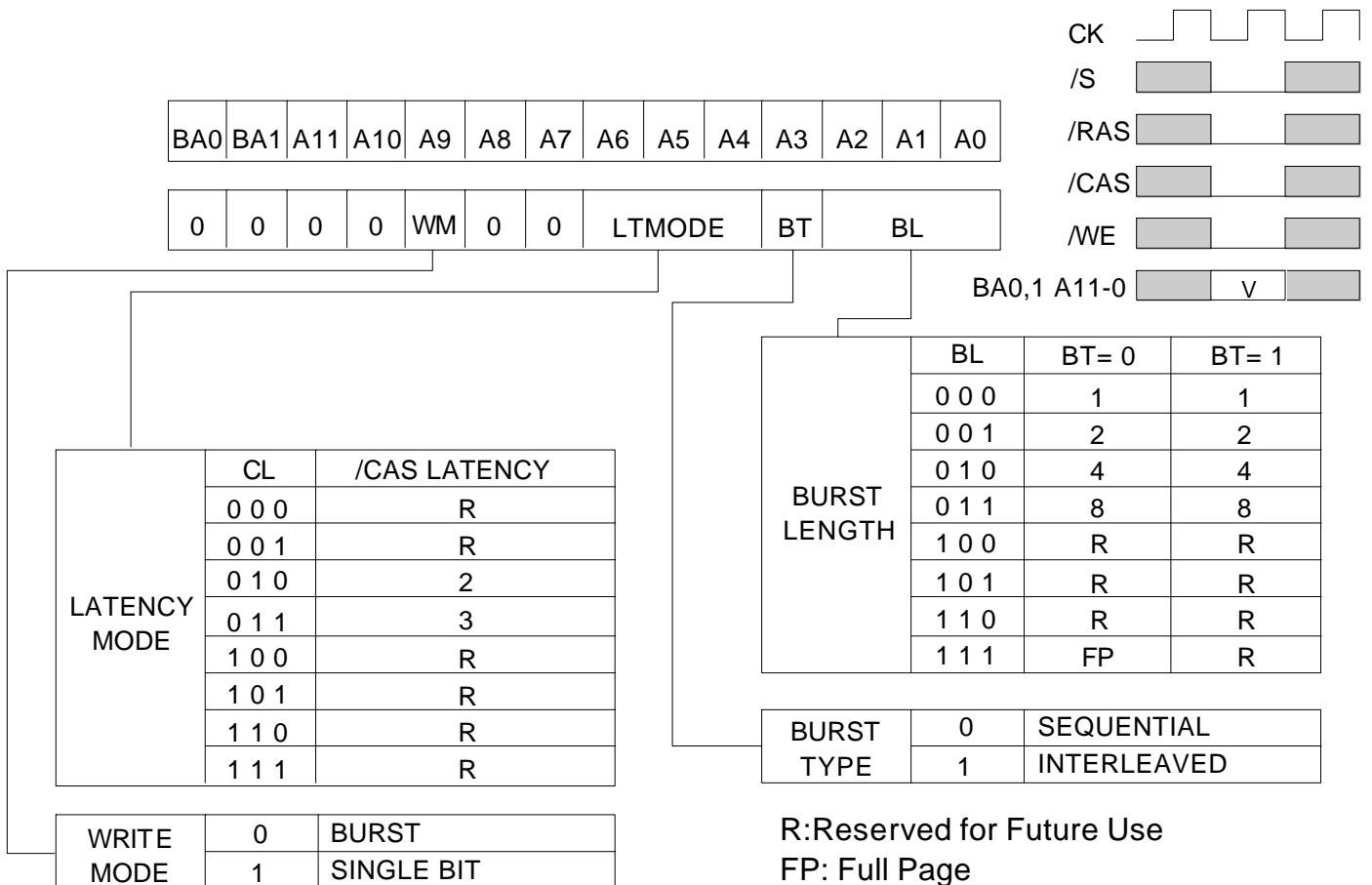
MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
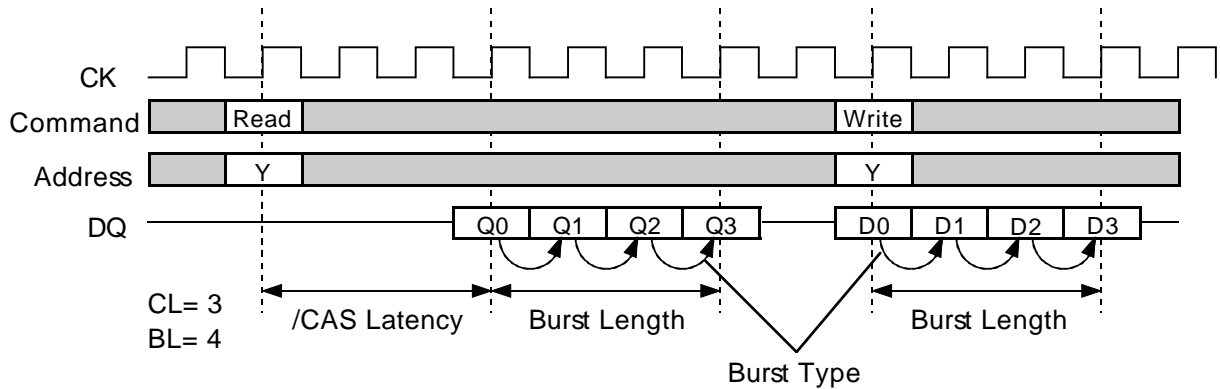
Initial Address			BL	Column Addressing																
A2	A1	A0		Sequential								Interleaved								
0	0	0	8	0	1	2	3	4	5	6	7	0	1	2	3	4	5	6	7
0	0	1		1	2	3	4	5	6	7	0	1	0	3	2	5	4	7	6
0	1	0		2	3	4	5	6	7	0	1	2	3	0	1	6	7	4	5
0	1	1		3	4	5	6	7	0	1	2	3	2	1	0	7	6	5	4
1	0	0		4	5	6	7	0	1	2	3	4	5	6	7	0	1	2	3
1	0	1		5	6	7	0	1	2	3	4	5	4	7	6	1	0	3	2
1	1	0		6	7	0	1	2	3	4	5	6	7	4	5	2	3	0	1
1	1	1		7	0	1	2	3	4	5	6	7	6	5	4	3	2	1	0
-	0	0	4	0	1	2	3					0	1	2	3				
-	0	1		1	2	3	0					1	0	3	2				
-	1	0		2	3	0	1					2	3	0	1				
-	1	1		3	0	1	2					3	2	1	0				
-	-	0	2	0	1							0	1						
-	-	1		1	0							1	0						

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

OPERATION DESCRIPTION

BANK ACTIVATE

One of four banks is activated by an ACT command.

An bank is selected by BA0-1. A row is selected by A0-11.

Multiple banks can be active state concurrently by issuing multiple ACT commands.

Minimum activation interval between one bank and another bank is tRRD.

PRECHARGE

An open bank is deactivated by a PRE command.

A bank to be deactivated is designated by BA0-1.

When multiple banks are active, a precharge all command (PREA, PRE + A10=H) deactivates all of open banks at the same time. BA0-1 are "Don't Care" in this case.

Minimum delay time of an ACT command after a PRE command to the same bank is tRP.

Bank Activation and Precharge All (BL=4, CL=2)

Precharge all
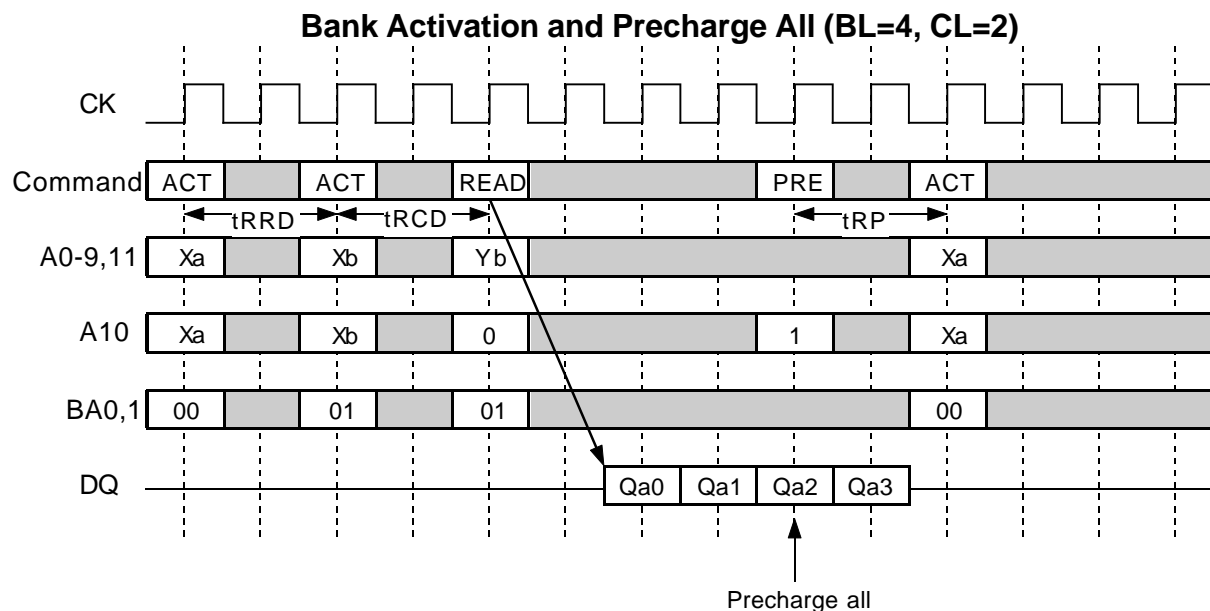
READ

A READ command can be issued to any active bank. The start address is specified by A0-9 (x8) . 1st output data is available after the /CAS Latency from the READ. The consecutive data length is defined by the Burst Length. The address sequence of the burst data is defined by the Burst Type. Minimum delay time of a READ command after an ACT command to the same bank is tRCD.

When A10 is high at a READ command, auto-precharge (READA) is performed. Any command (READ, WRITE, PRE, ACT, TBST) to the same bank is inhibited till the internal precharge is complete. The internal precharge starts at the BL after READA. The next ACT command can be issued after (BL + tRP) from the previous READA. In any case, tRCD+BL $\geq$ tRASmin must be met.

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Multi Bank Interleaving READ (BL=4, CL=2)

READ with Auto-Precharge (BL=4, CL=2)

Internal precharge starts
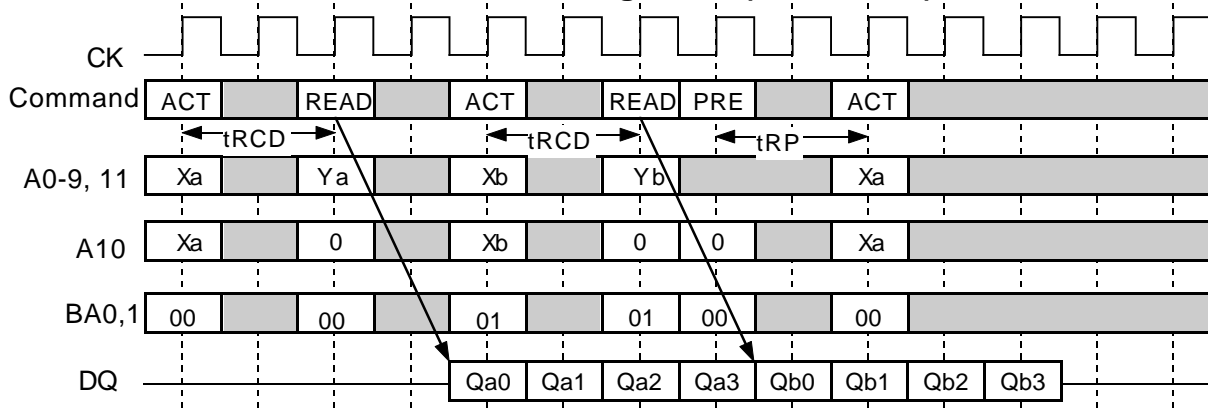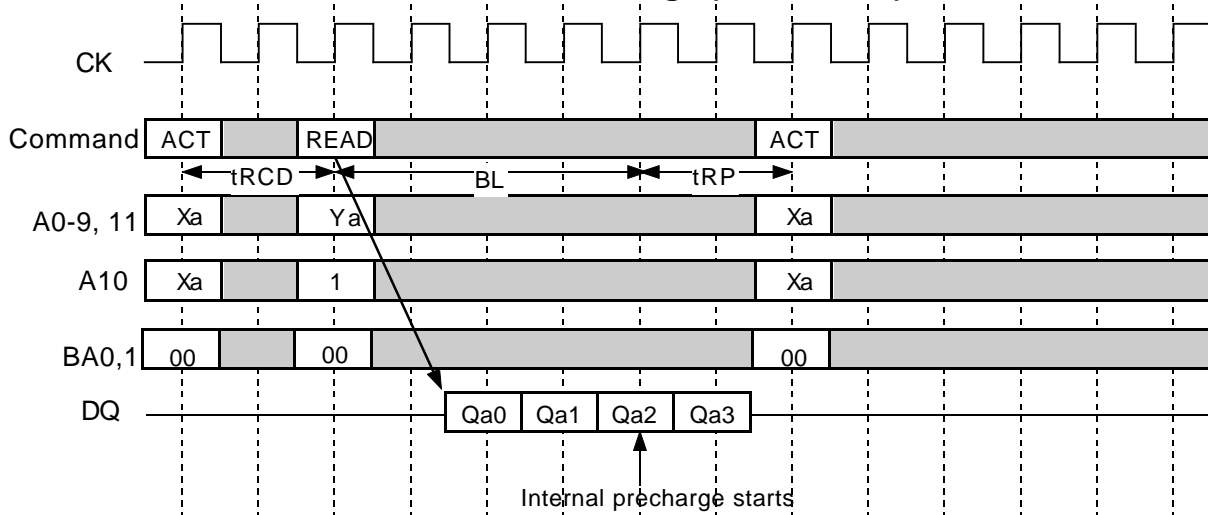
Auto-Precharge Timing (READ BL=4)

Internal precharge starts

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
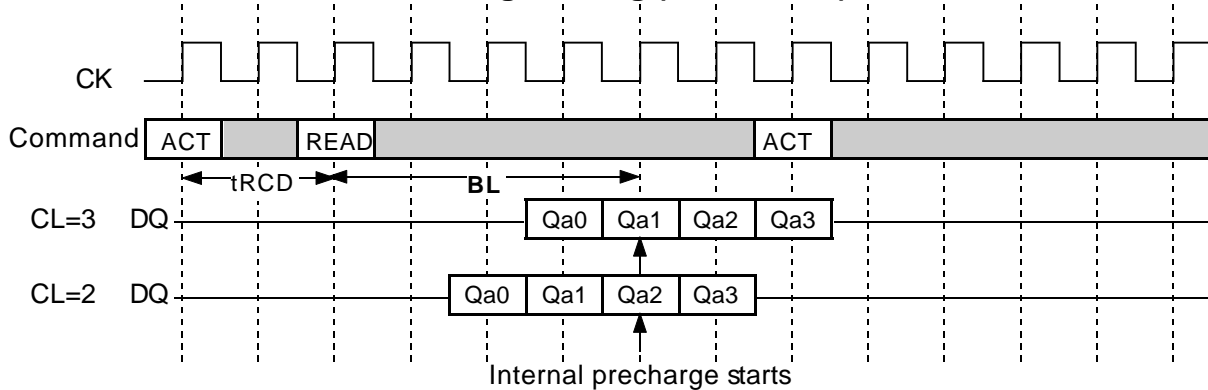
MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

WRITE

A WRITE command can be issued to any active bank. The start address is specified by A0-9 (x8). 1st input data is set at the same cycle as the WRITE. The consecutive data length to be written is defined by the Burst Length. The address sequence of burst data is defined by the Burst Type. Minimum delay time of a WRITE command after an ACT command to the same bank is tRCD. From the last input data to the PRE command, the write recovery time (tWR) is required. When A10 is high at a WRITE command, auto-precharge (WRITEA) is performed. Any command (READ, WRITE, PRE, ACT, TBST) to the same bank is inhibited till the internal precharge is complete. The internal precharge starts at tWR after the last input data cycle. The next ACT command can be issued after (BL + tWR -1 + tRP) from the previous WRITEA. In any case, tRCD + BL + tWR -1 $\geq$ tRASmin must be met.

WRITE (BL=4)

WRITE with Auto-Precharge (BL=4)

Internal precharge begins

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
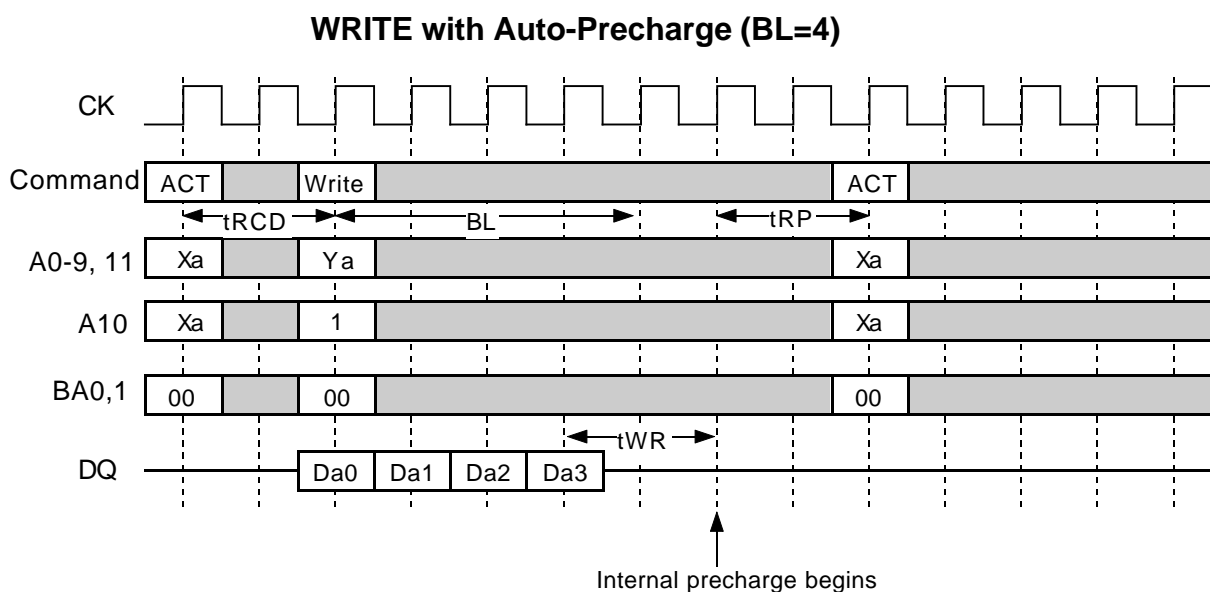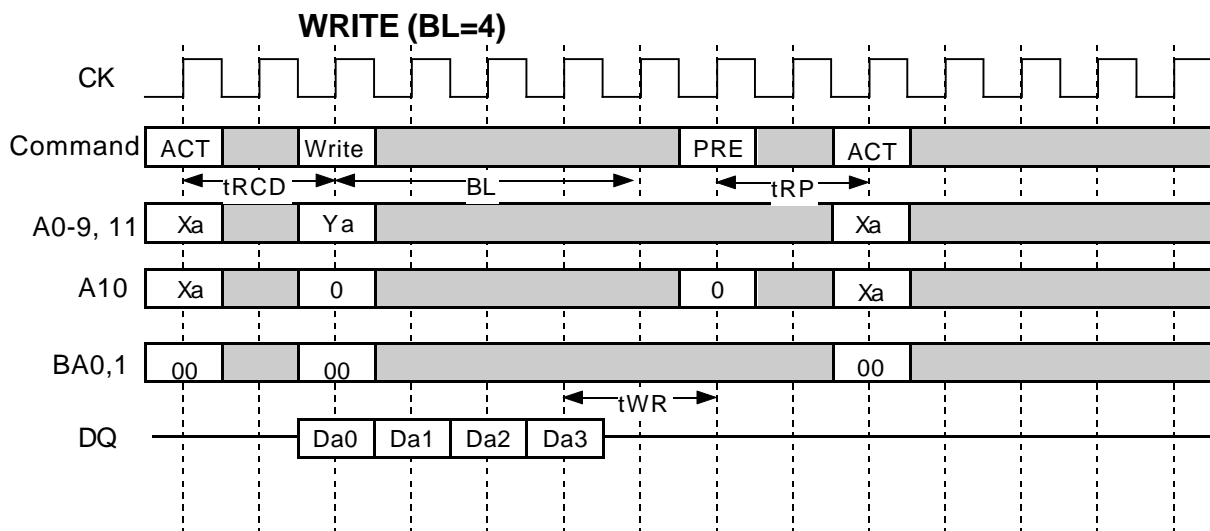
MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

BURST INTERRUPTION
[Read Interrupted by Read]

Burst read oparation can be interrupted by new read of the same or the other bank. Random column access is allowed READ to READ interval is minimum 1 CK

Read Interrupted by Read (BL=4, CL=2)
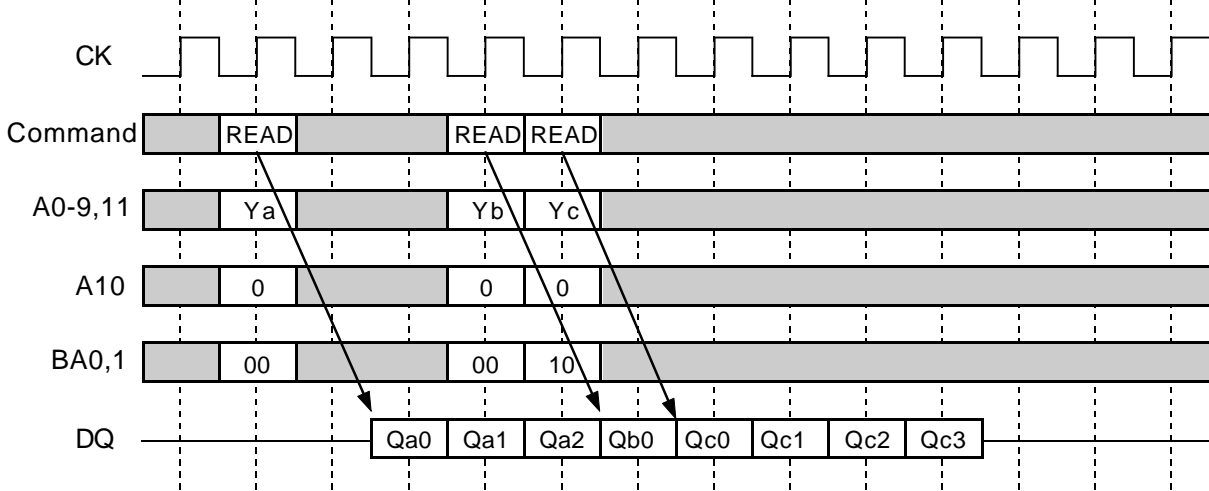
[Read Interrupted by Write]

Burst read operation can be interrupted by write of any active bank. Random column access is allowed. In this case, the DQ should be controlled adequately by using the DQMB0-7 to prevent the bus contention. The output is disabled automatically 1 cycle after WRITE assertion.

Read Interrupted by Write (BL=4, CL=2)
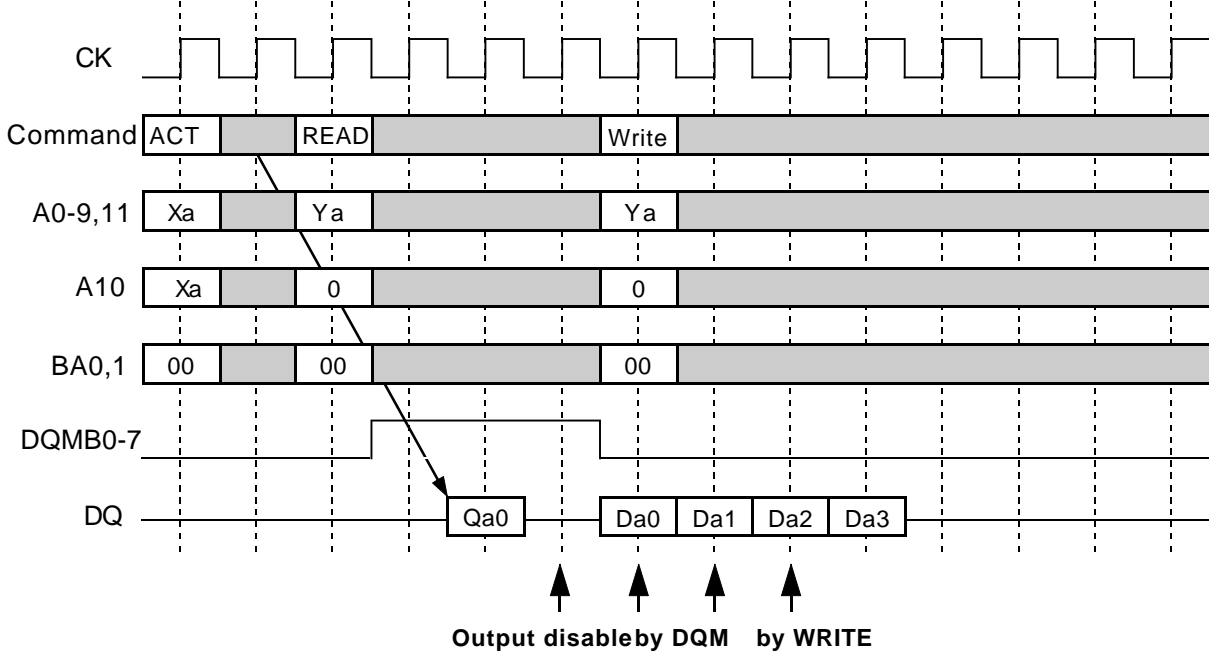
Output disable by DQM by WRITE

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

[Read Interrupted by Precharge]

A burst read operation can be interrupted by precharge of *the same bank*. Read to PRE interval is minimum 1 CK. A PRE command output disable latency is equivalent to the /CAS Latency.

Read Interrupted by Precharge (BL=4)

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
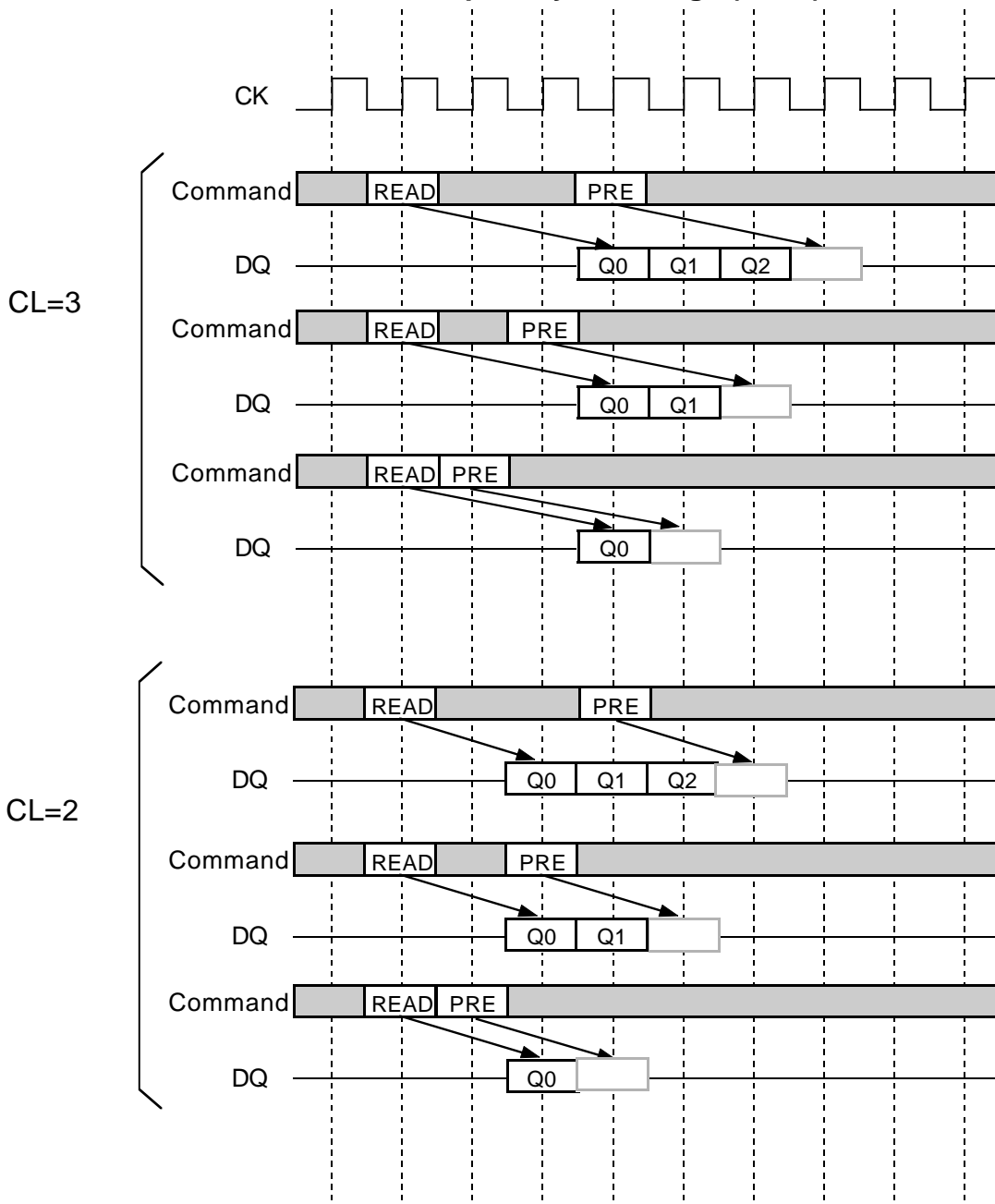
MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

[Read Interrupted by Burst Terminate]

Similarly to the precharge, burst terminate command can interrupt burst read operation and disable the data output. The terminated bank remains active,READ to TBST interval is minimum of 1 CK. A TBSTcommand to output disable latency is equivalent to the /CAS Latency.
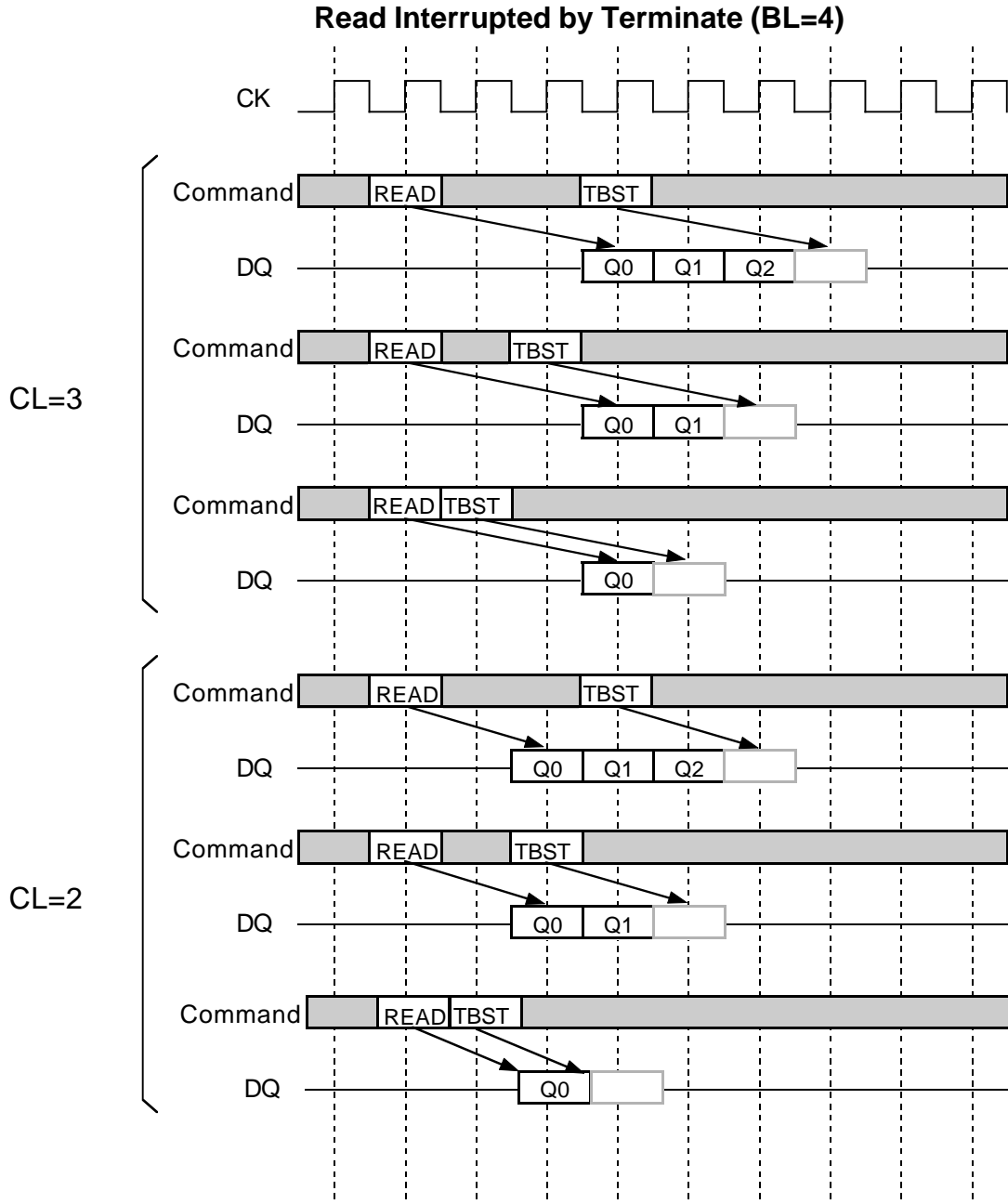
Read Interrupted by Terminate (BL=4)

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

[Write Interrupted by Write]

Burst write operation can be interrupted by new write of any active bank. Random column access is allowed. WRITE to WRITE interval is minimum 1 CK.

Write Interrupted by Write (BL=4)
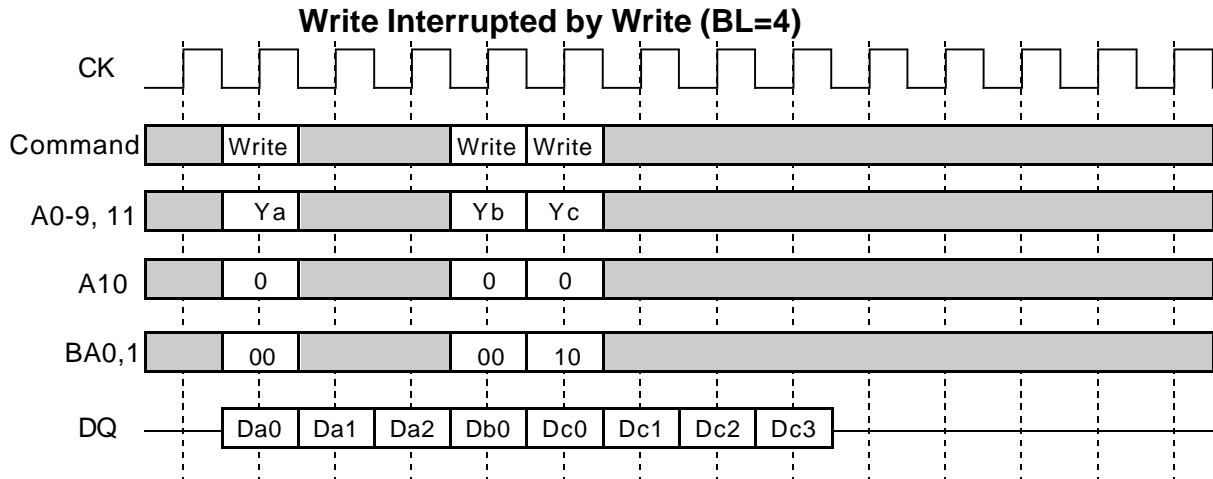
[Write Interrupted by Read]

Burst write operation can be interrupted by read of any active bank. Random column access is allowed. WRITE to READ interval is minimum 1 CK. The input data on DQ at the interrupting READ cycle is "don't care".

Write Interrupted by Read (BL=4, CL=2)

don't care

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
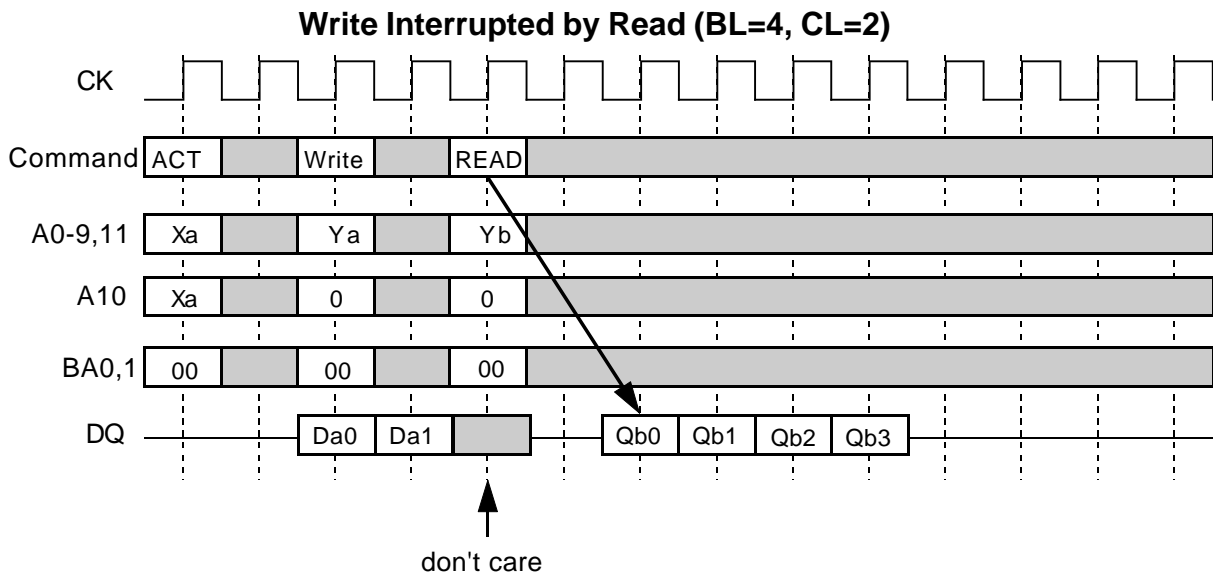
[Write Interrupted by Precharge]

Burst write operation can be interrupted by precharge of *the same bank*. Write recovery time(tWR) is required from the last data to PRE command. During write recovery, data inputs must be masked by DQM.

Write Interrupted by Precharge (BL=4)
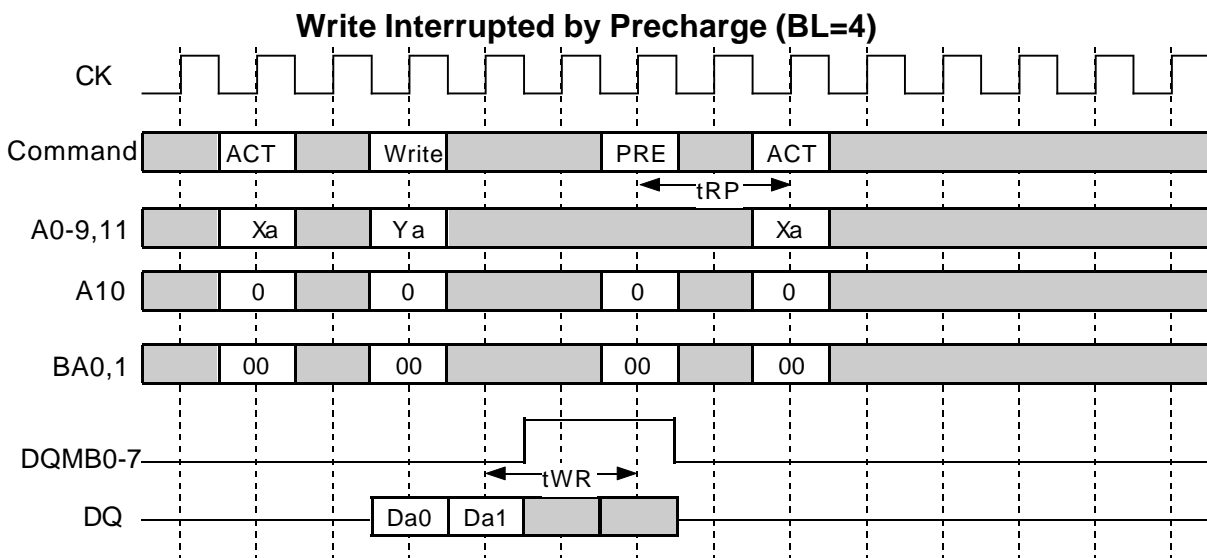
[Write Interrupted by Burst Terminate]

Burst terminate command can terminate burst write operation. In this case, the write recovery time is not required and the bank remains active.The WRITE to TBST minimum interval is 1CK.

Write Interrupted by Burst Terminate (BL=4)

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
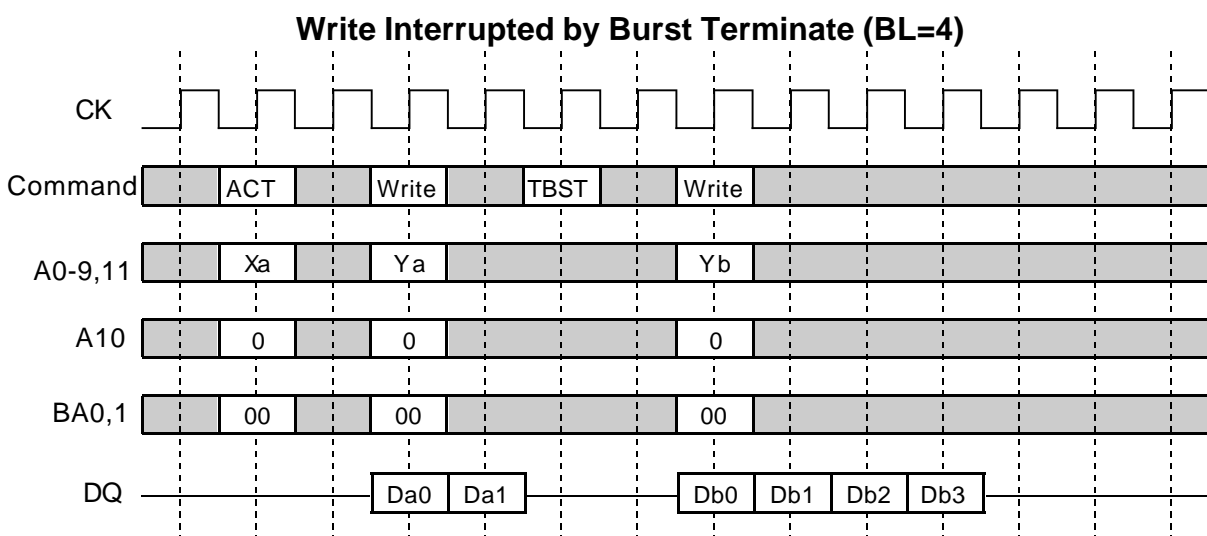
MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

[Write with Auto-Precharge interrupted by Write or Read to anotehr Bank]
Burst write with auto-precharge can be interrupted by write or read to *another bank*.
Next ACT command can be issued after (BL+tWR-1+tRP) from the WRITEA. Auto-precharge interrrupted by a command to the same bank is inhibited.

WRITEA Interrupted by WRITE to another bank (BL=4)
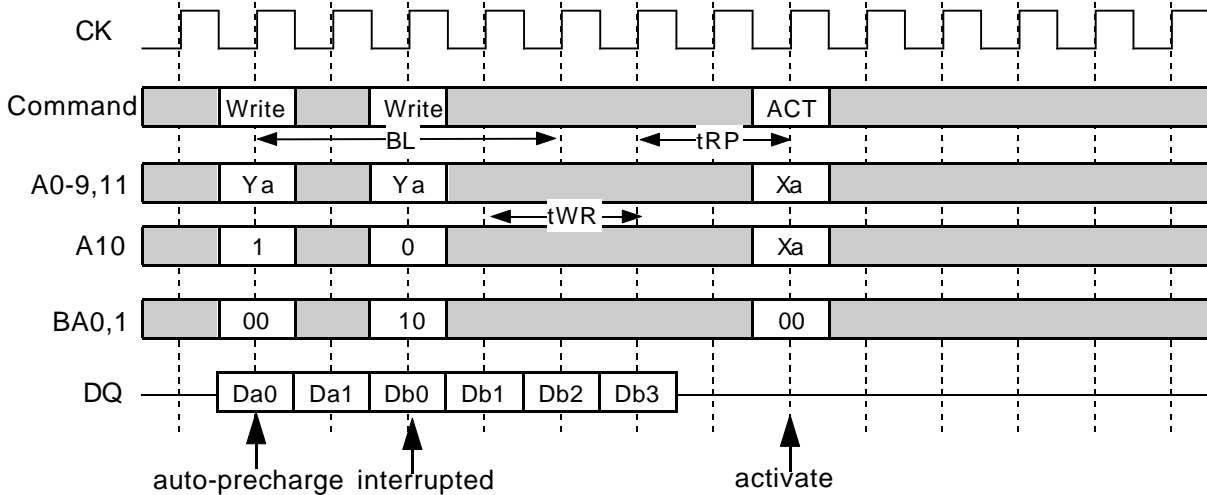
WRITEA interrupted by READ to another bank (CL=2,BL=4)

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
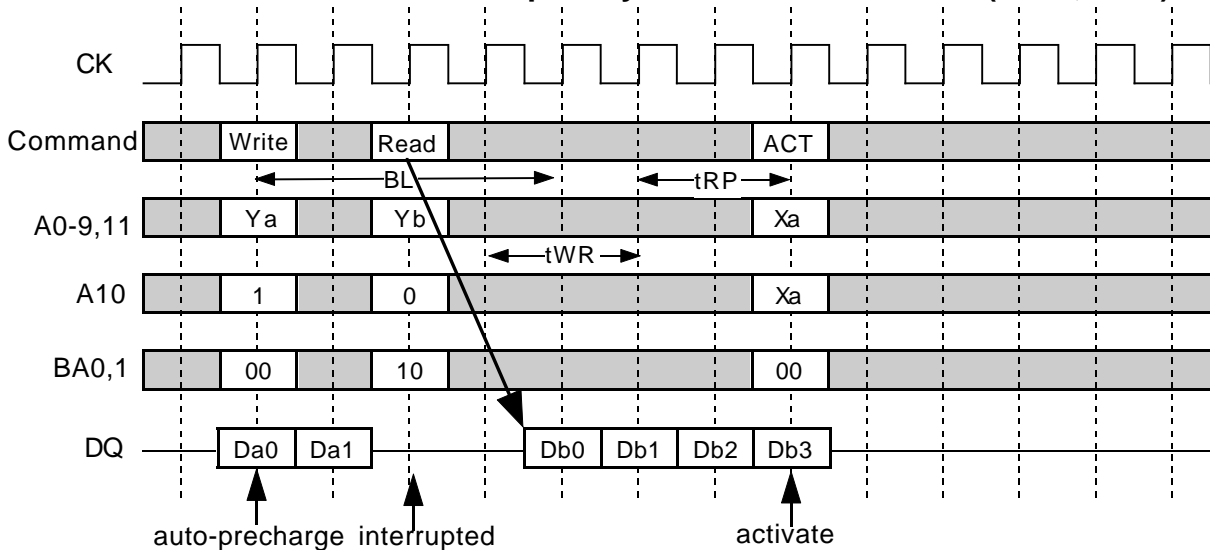
[Read with Auto-Precharge interrupted by Read to anotehr Bank]

Burst read with auto-precharge can be interrupted by read to *another bank*. Next ACT command can be issued after (BL+tRP) from the READA. Auto-precharge interrrupted by a command to the same bank is inhibited.

READA Interrupted by READ to another bank (CL=2,BL=4)
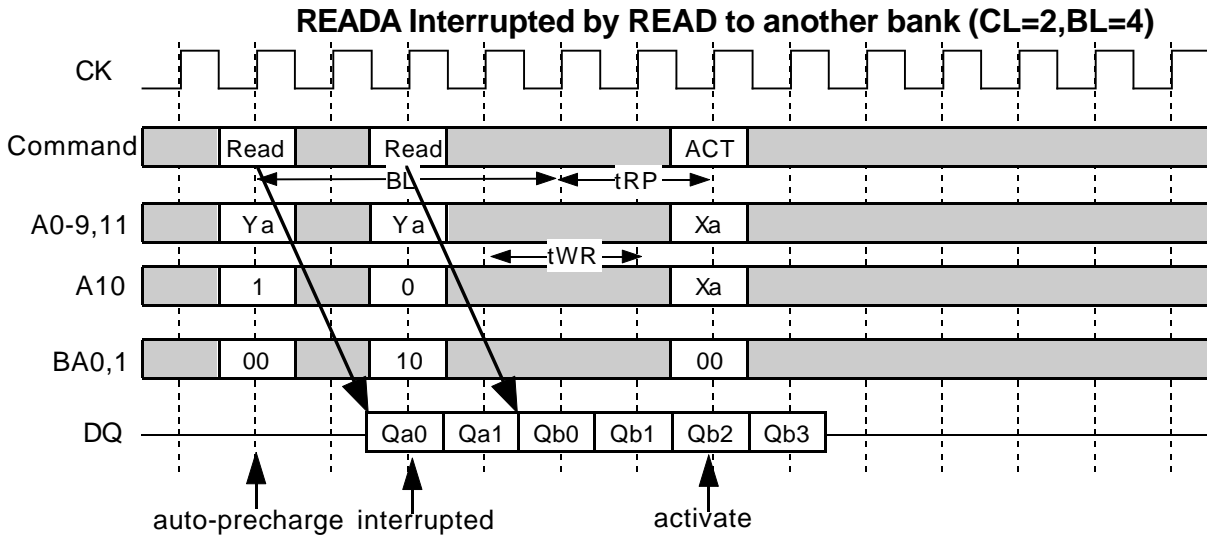
Full Page Burst

Full page burst length is available for only the sequential burst type. Full page burst read or write is repeated untill aPrecharge or a Burst Terminate command is issued. In case of the full page burst , a read or write with auto-precharge command is illegal.

Single Write

When single write mode is set, burst length for write is always one, independently of Burst Length defined by (A2-0).

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

AUTO REFRESH

Single cycle of auto-refresh is initiated with a REFA(/CS=/RAS=/CAS=L, /WE=/CKE=H) command. The refresh address is generated internally. 4096 REFA cycle within 64ms refresh 128Mbit memory cells. The auto-refresh is performed on 4banks concurrently. Before performing an auto-refresh, all banks must be in the idle state. Auto-refresh to auto-refresh interval is minimum tRFC. Any command must not be issued before tRFC from the REFA command.
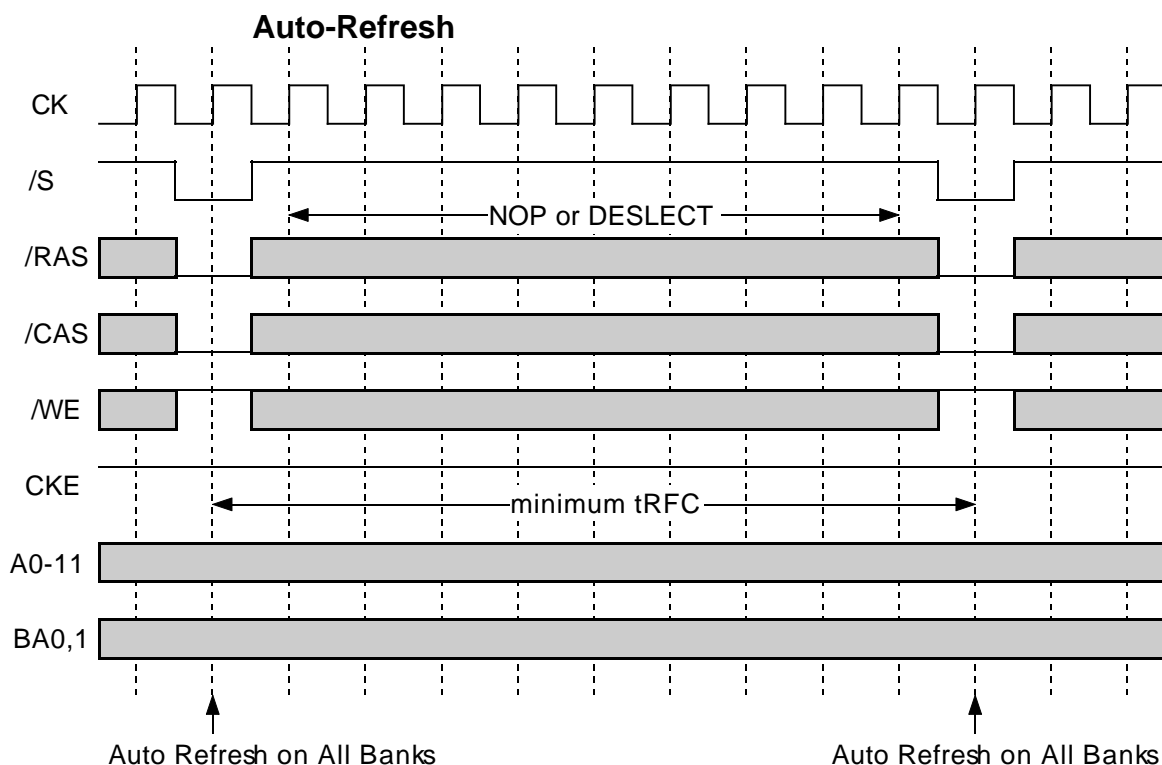
Auto-Refresh

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

SELF REFRESH

Self-refresh mode is entered by issuing a REFS command (/CS=/RAS=/CAS=L, /WE=H, CKE=L). Once the self-refresh is initiated, it is maintained as log as CKE is kept low.During the self-refresh mode, CKE is asynchronous and the only enabled input , all other inputs including CK are disabled and ignored, so that power consumption due to synchronous inputs is saved. To exit the self-refresh, supplying stable CK inputs, asserting DESEL or NOP command and then asserting CKE=H. After tRFC from the 1st CK edge follwing CKE=H, all banks are in the idle state and a new command can be issued after, but DESEL or NOP commands must be asserted till then.

Self-Refresh

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
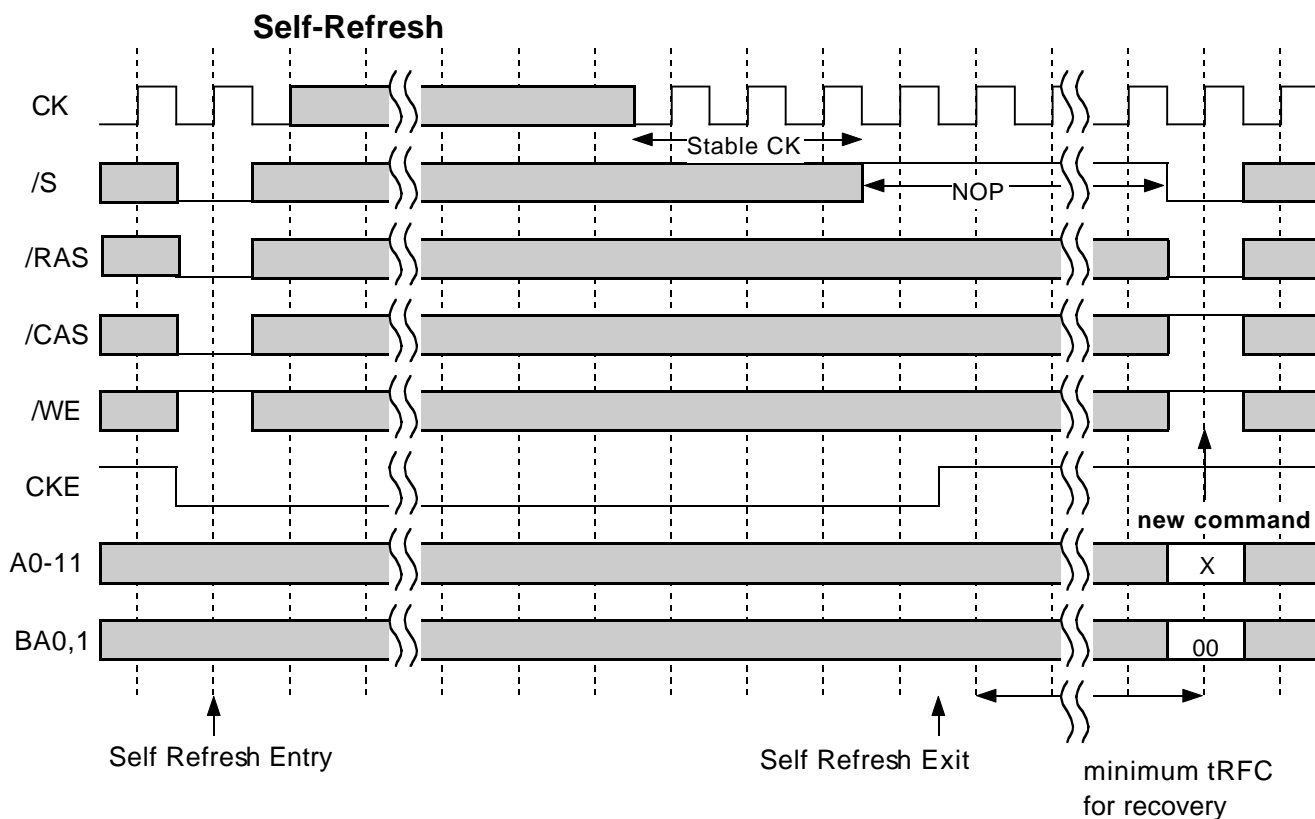
CLK SUSPEND and POWER DOWN

 CKE controls the internal CLK at the following cycle. Figure below shows how CKE works. By negating CKE, the next internal CLK is suspended. The purpose of CLK suspend is power down, output suspend or input suspend. CKE is a synchronous input except during the self-refresh mode. CLK suspend can be performed either when the banks are active or idle. A command at the suspended cycle is ignored.
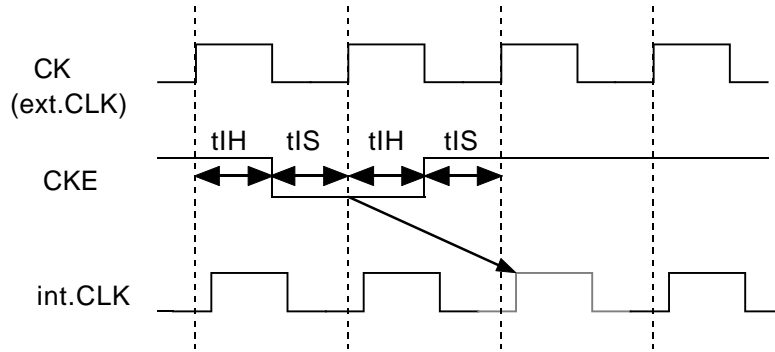
Power Down by CKE
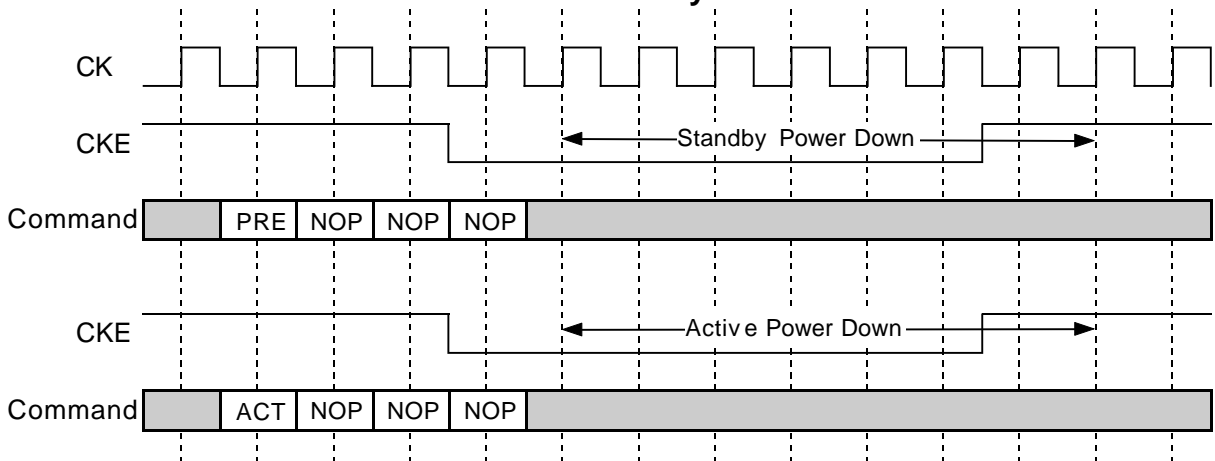
DQ Suspend by CKE

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
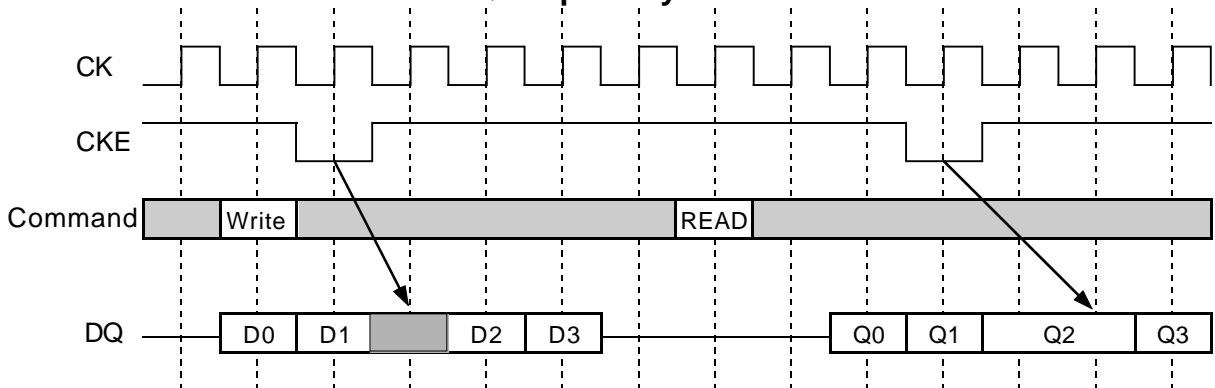
MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

DQM CONTROL

DQMB0-7 is a dual function signal defined as the data mask for writes and the output disable for reads. During writes, DQMB0-7 masks input data word by word. DQMB0-7 to Data In latency is 0.

During reads, DQMB0-7 forces output to Hi-Z word by word. DQMB0-7 to output Hi-Z latency is 2.

DQM Function

masked by DQMB=H

disabled by DQMB=H

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
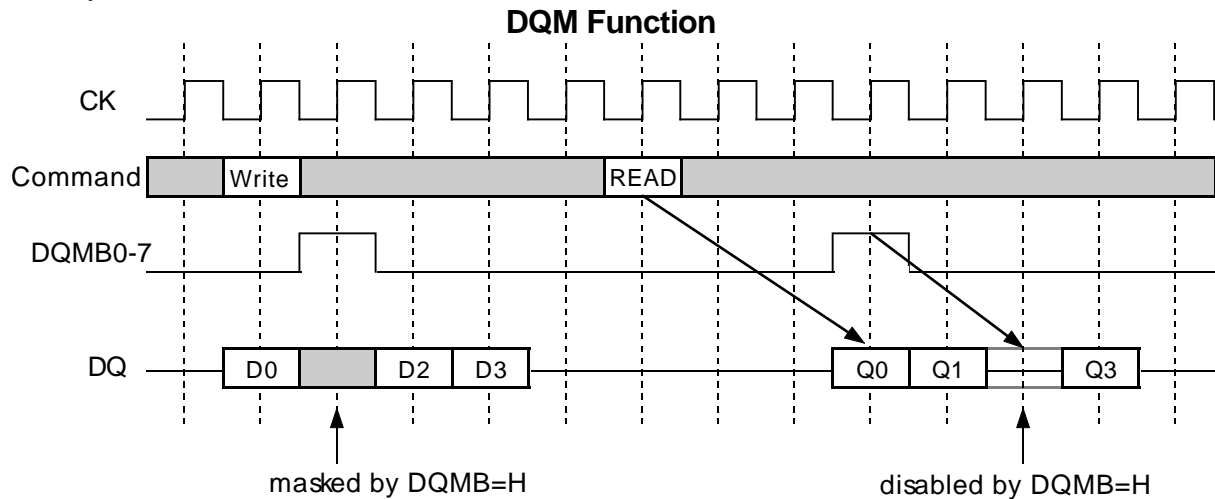
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Condition	Ratings	Unit
Vdd	Supply Voltage	with respect to Vss	-0.5 ~ 4.6	V
VI	Input Voltage	with respect to Vss	-0.5 ~ Vdd+0.5	V
VO	Output Voltage	with respect to Vss	-0.5 ~ Vdd+0.5	V
IO	Output Current		50	mA
Pd	Power Dissipation	Ta=25°C	9	W
Topr	Operating Temperature		0 ~ 70	°C
Tstg	Storage Temperature		-40 ~ 100	°C

RECOMMENDED OPERATING CONDITION

(Ta=0 ~ 70°C, unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
Vdd	Supply Voltage	3.0	3.3	3.6	V
Vss	Supply Voltage	0	0	0	V
VIH	High-Level Input Voltage all inputs	2.0		Vdd+0.3	V
VIL	Low-Level Input Voltage all inputs	-0.3		0.8	V

Note)
1:VIH(max)=5.5V for pulse width less than 10ns.
2.VIL(min)=-1.0 for pulse width less than 10ns.

CAPACITANCE

(Ta=0 ~ 70°C, Vdd = 3.3 ± 0.3V, Vss = 0V, unless otherwise noted)

Symbol	Parameter	Test Condition	Limits(max.)	Unit
CI(A)	Input Capacitance, address pin	@1MHz 1.4V bias 200mV swing	60	pF
CI(C)	Input Capacitance, /RAS,/CAS,/WE		60	pF
CI(K)	Input Capacitance, CK pin		40	pF
CI/O	Input Capacitance, I/O pin		16.5	pF

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

AVERAGE SUPPLY CURRENT from Vdd

(Ta=0 ~70°C, Vdd = 3.3 ± 0.3V, Vss = 0V, unless otherwise noted)

Parameter	Symbol	Test Condition	Limits (max)		Unit
			-6	-7, -8	
operating current one bank active (discrete)	Icc1	tRC=min.tCLK=min, BL=1,CL=3	990	900	mA
precharge stanby current in power-down mode	Icc2P	CKE=L,tCLK=15ns, /CS>Vcc-0.2V	36	36	mA
	Icc2PS	CKE=CLK=L, /CS>Vcc-0.2V	18	18	mA
precharge stanby current in non power-down mode	Icc2N	CKE=H,tCLK=15ns,VIH>Vcc-0.2V,VIL<0.2V	225	225	mA
	Icc2NS	CKE=H,CLK=L,VIH>Vcc-0.2V,VIL<0.2V(fixed)	135	135	mA
active stanby current in non power-down mode one bank active (discrete)	Icc3N	CKE=H,tCLK=15ns	270	270	mA
	Icc3NS	CKE=H,CLK=L	180	180	mA
burst current	Icc4	tCLK=min, BL=4, CL=3,all banks active(discerte)	1350	1080	mA
auto-refresh current	Icc5	tRC=min, tCLK=min	1440	1440	mA
self-refresh current	Icc6	CKE <0.2V	18	18	mA

Note)
1:Icc(max) is specified at the output open condition.

AC OPERATING CONDITIONS AND CHARACTERISTICS

(Ta=0 ~ 70°C, Vdd = 3.3 ± 0.3V, Vss = 0V, unless otherwise noted)

Symbol	Parameter	Test Condition	Limits Min.	Max.	Unit
VOH(DC)	High-Level Output Voltage(DC)	IOH=-2mA	2.4		V
VOL(DC)	Low-Level Output Voltage(DC)	IOL=2mA		0.4	V
IOZ	Off-stare Output Current	Q floating VO=0 ~ Vdd	-10	10	uA
Ii	Input Current	VIH=0 ~ Vdd+0.3V	-90	90	uA

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
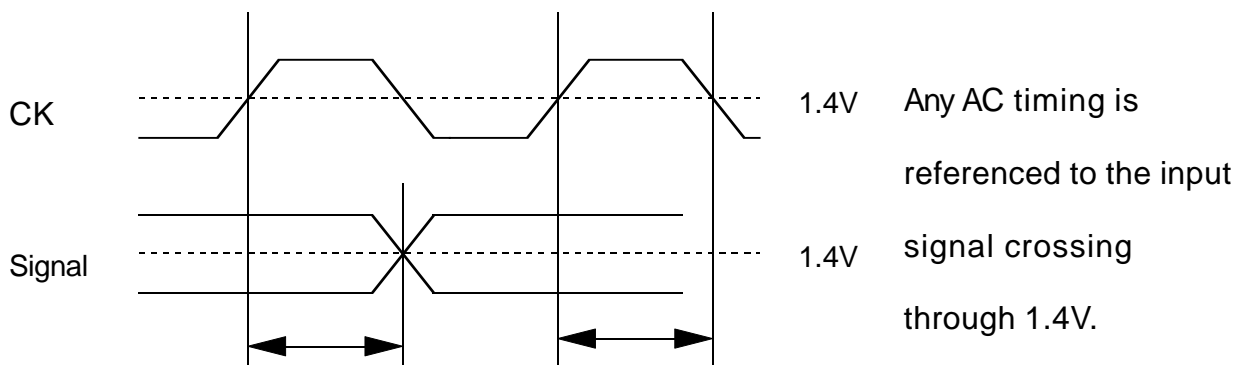1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

AC TIMING REQUIREMENTS (SDRAM Component)

(Ta=0 ~ 70°C, Vdd = 3.3 ± 0.3V, Vss = 0V, unless otherwise noted)
Input Pulse Levels: 0.8V to 2.0V
Input Timing Measurement Level: 1.4V

Symbol	Parameter		Limits						Unit
			-6		-7		-8		
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{CLK}	CK cycle time	CL=2	10		10		13		ns
		CL=3	7.5		10		10		ns
t_{CH}	CK High pulse width		2.5		3		3		ns
t_{CL}	CK Low pilse width		2.5		3		3		ns
t_T	Transition time of CK		1	10	1	10	1	10	ns
t_{IS}	Input Setup time(all inputs)		1.5		2		2		ns
t_{IH}	Input Hold time(all inputs)		0.8		1		1		ns
t_{RC}	Row cycle time		67.5		70		70		ns
t_{RCD}	Row to Column Delay		20		20		20		ns
t_{RAS}	Row Active time		45	100K	50	100K	50	100K	ns
t_{RP}	Row Precharge time		20		20		20		ns
t_{WR}	Write Recovery time		15		20		20		ns
t_{RRD}	Act to Act Deley time		15		20		20		ns
t_{RSC}	Mode Register Set Cycle time		15		20		20		ns
t_{SRX}	Self Refresh Exit time		7.5		10		10		ns
t_{PDE}	Power Down Exit time		7.5		10		10		ns
t_{REF}	Refresh Interval time			64		64		64	ms

CK   1.4V   Any AC timing is

Signal   1.4V   referenced to the input

signal crossing

through 1.4V.

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

SWITCHING CHARACTERISTICS (SDRAM Component)

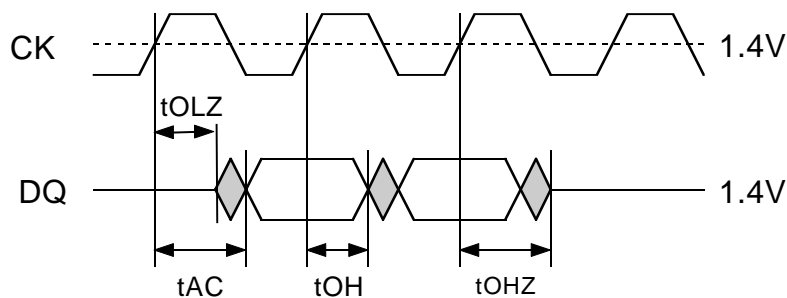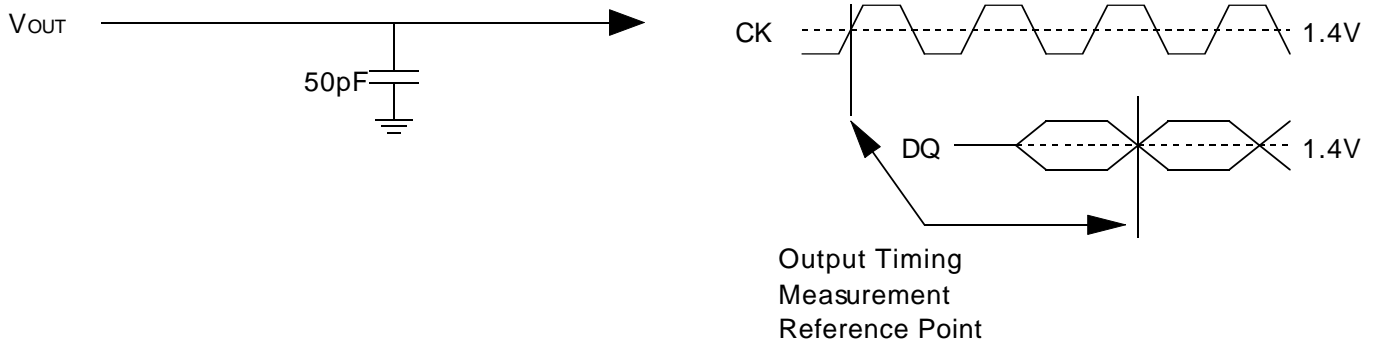(Ta=0 ~ 70°C, Vdd = 3.3 ± 0.3V, Vss = 0V, unless otherwise note3)

Symbol	Parameter		-6 Min.	-6 Max.	-7 Min.	-7 Max.	-8 Min.	-8 Max.	Unit
tAC	Access time from CK	CL=2		6		6		7	ns
		CL=3		5.4		6		6	ns
tOH	Output Hold time from CK	CL=2	3		3		3		ns
		CL=3	2.7		3		3		ns
tOLZ	Delay time, output low impedance from CK		0		0		0		ns
tOHZ	Delay time, output high impedance from CK		2.7	5.4	3	6	3	6	ns

Note)
1 If clock rising time is longer than 1ns,(tT/2-0.5)ns should be added to parameter.

Output Load Condition

V$_{OUT}$

50pF

CK ———— 1.4V

DQ ———— 1.4V

Output Timing
Measurement
Reference Point

CK ———— 1.4V

tOLZ

DQ ———— 1.4V

tAC   tOH   tOHZ

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
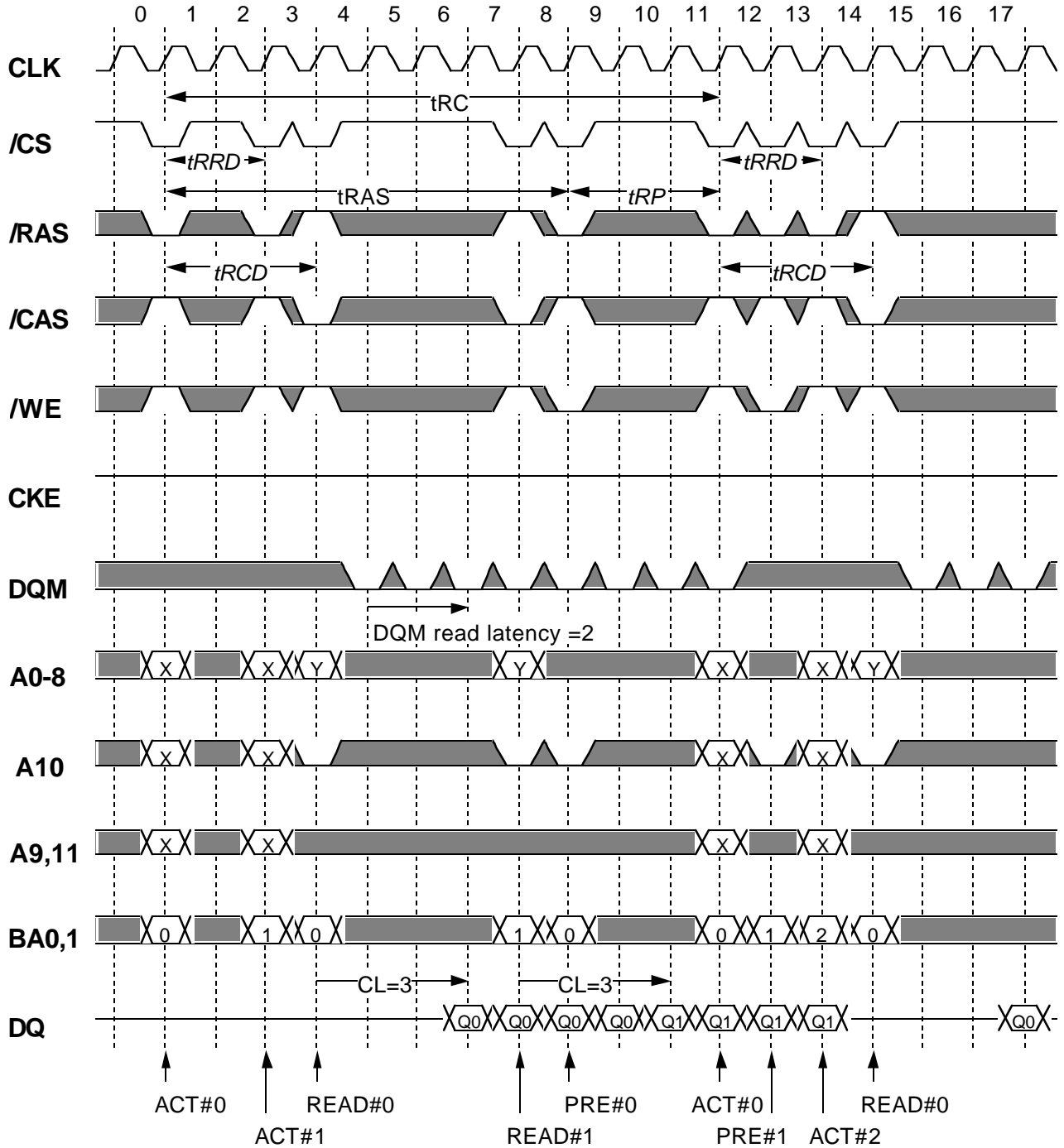
Burst Write (single bank) @BL=4
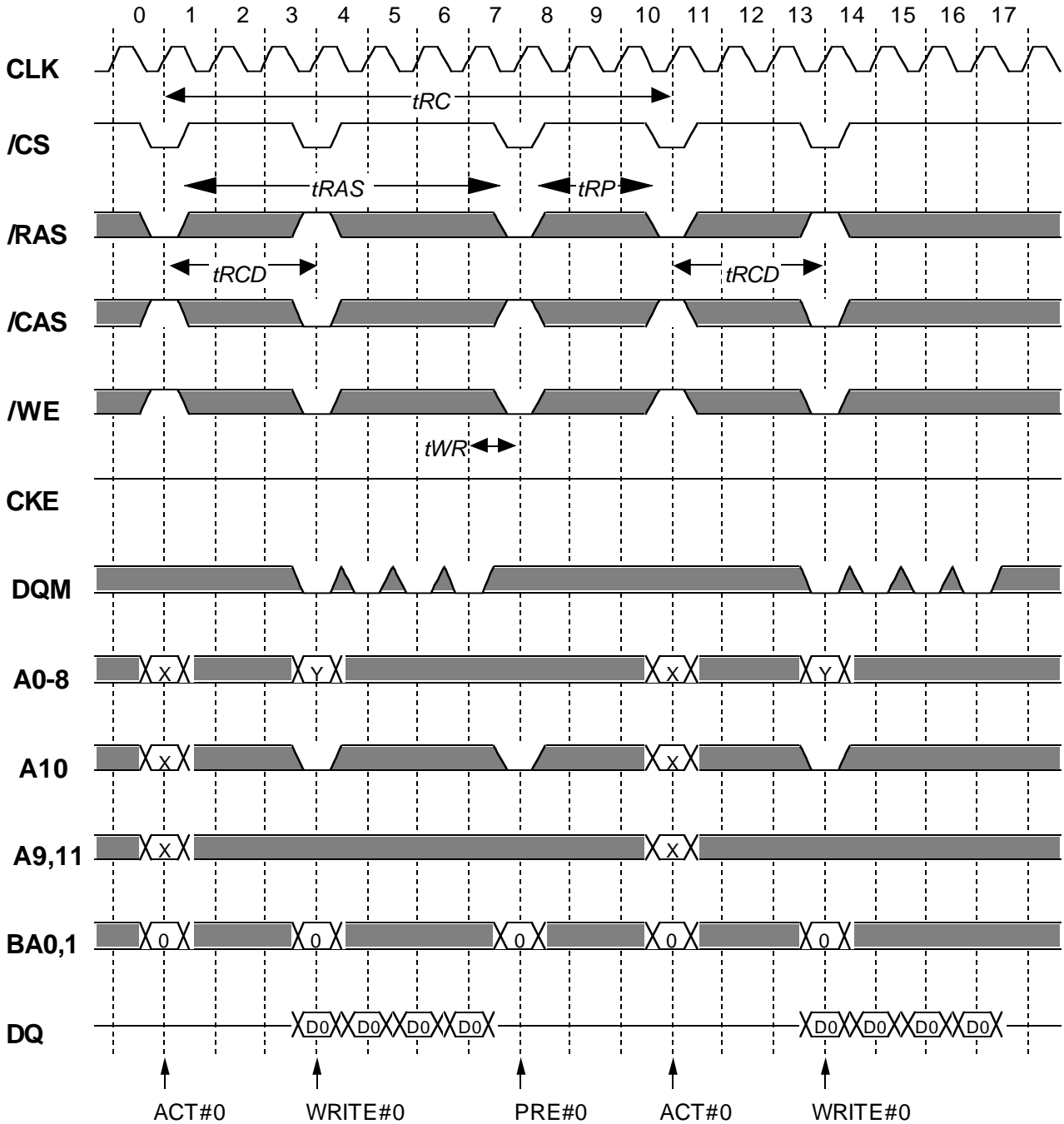
Italic parameter indicates minimum case
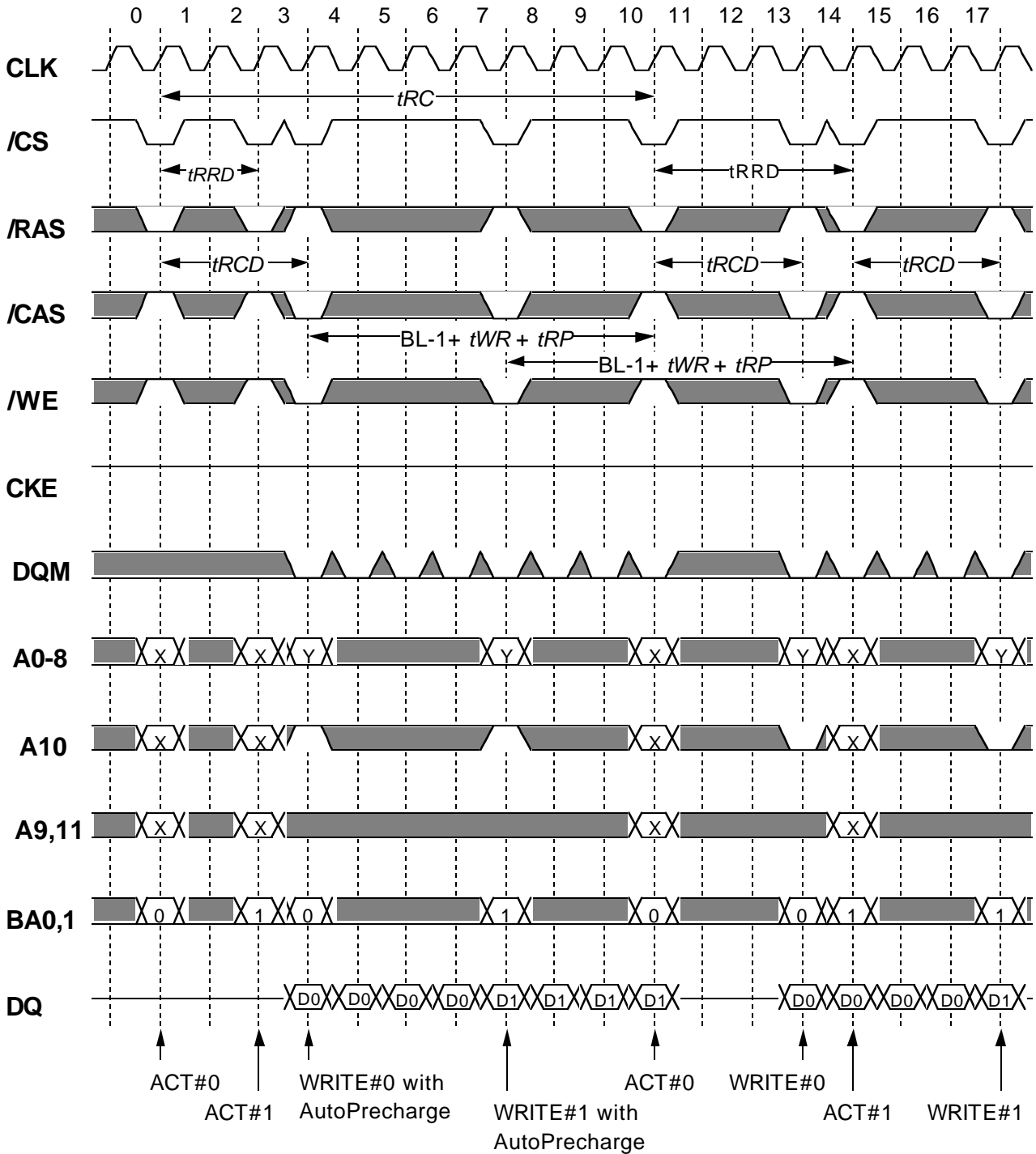
Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Burst Write (multi bank) @BL=4

Italic parameter indicates minimum case
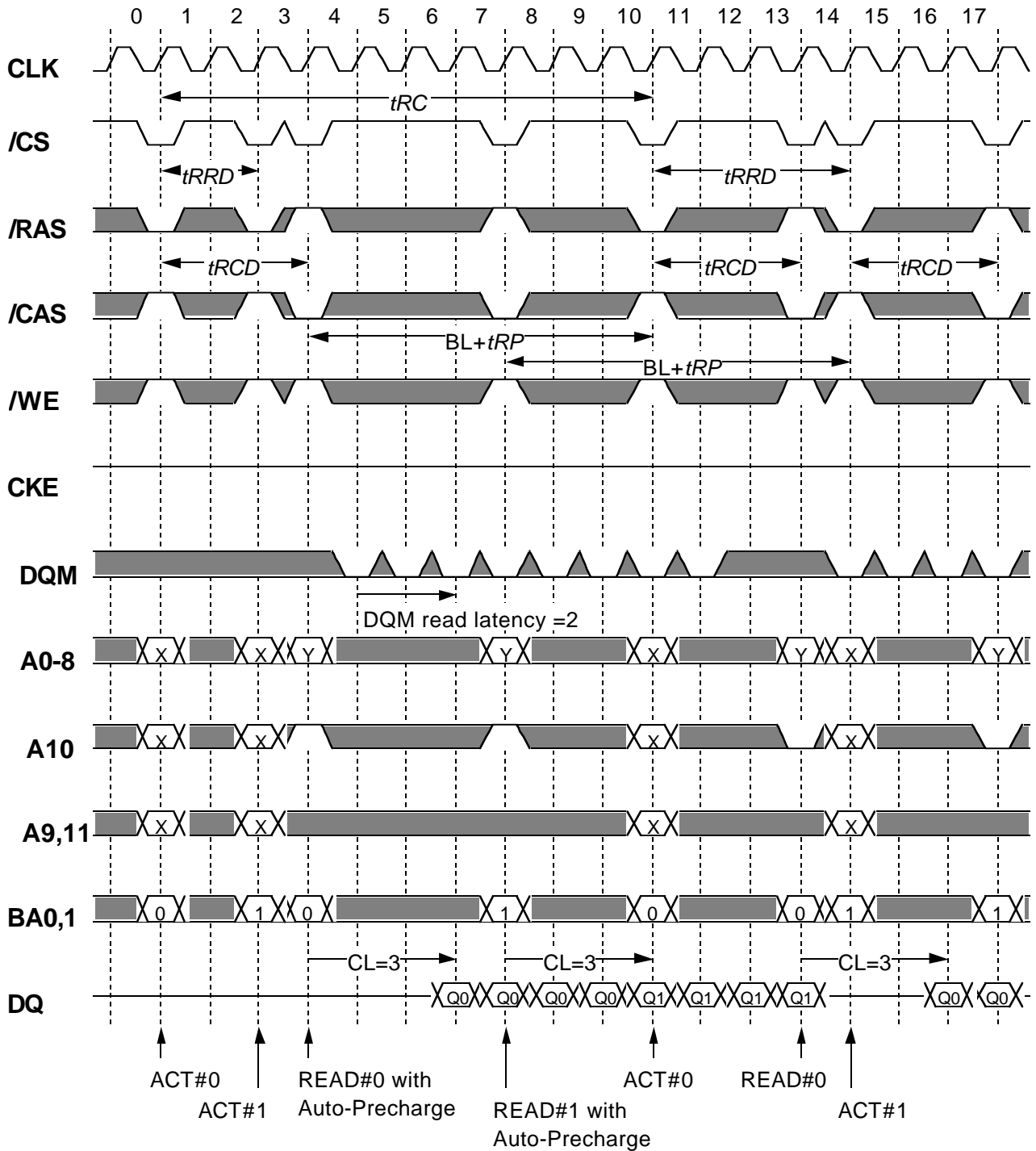
Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
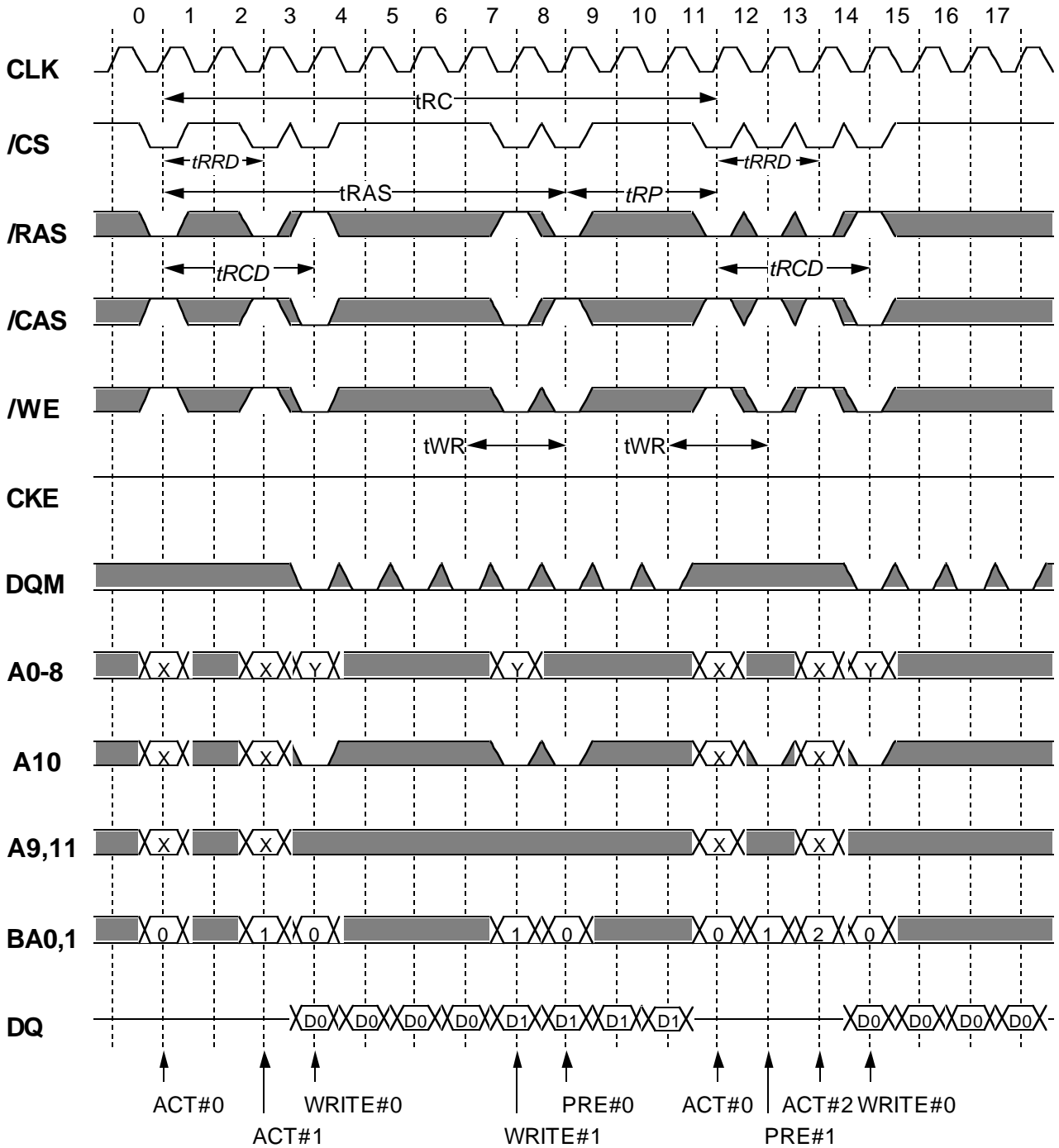
MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Burst Read (single bank) @BL=4 CL=3
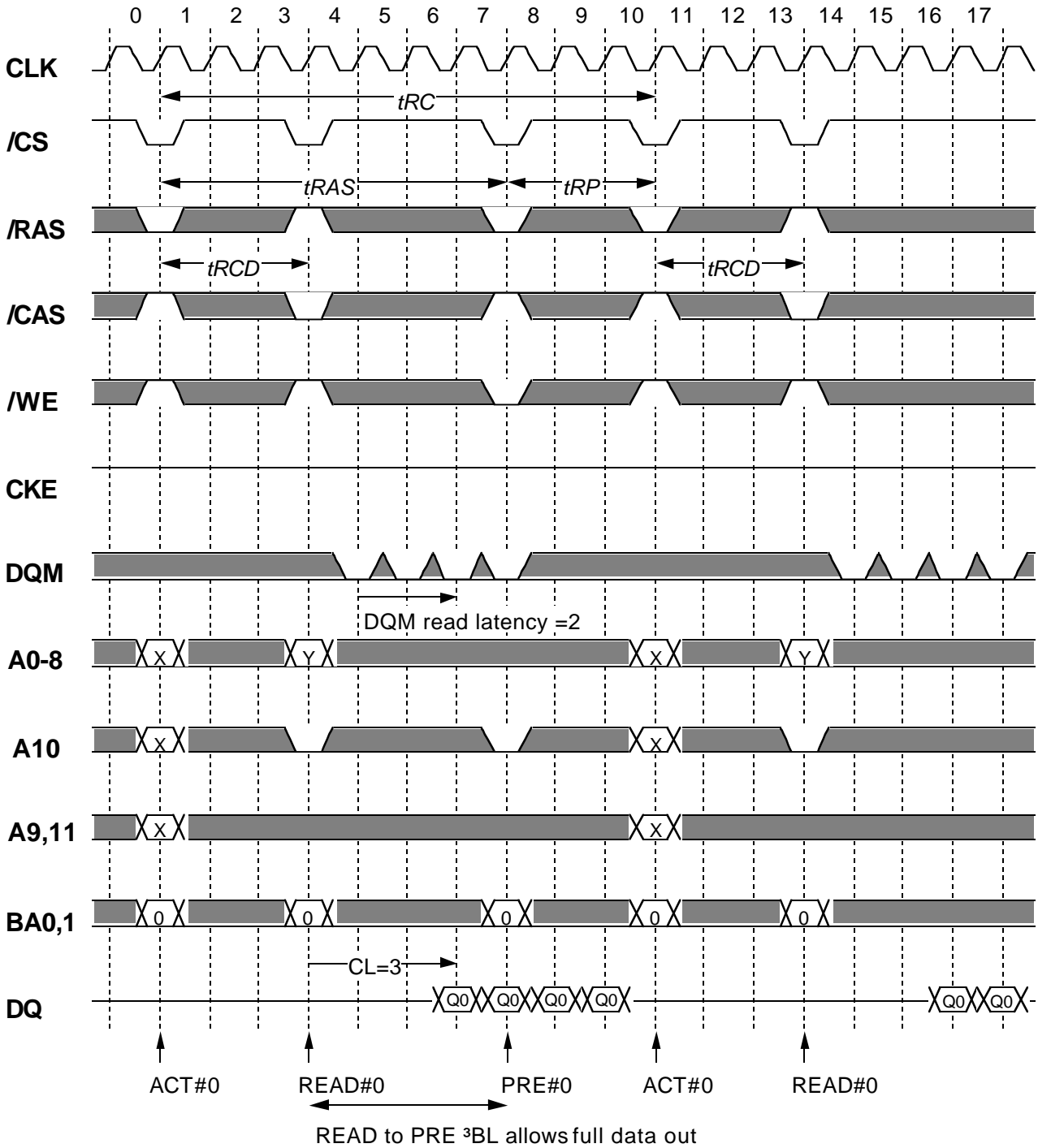
READ to PRE ³BL allows full data out

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Burst Read (multiple bank) @BL=4 CL=3

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

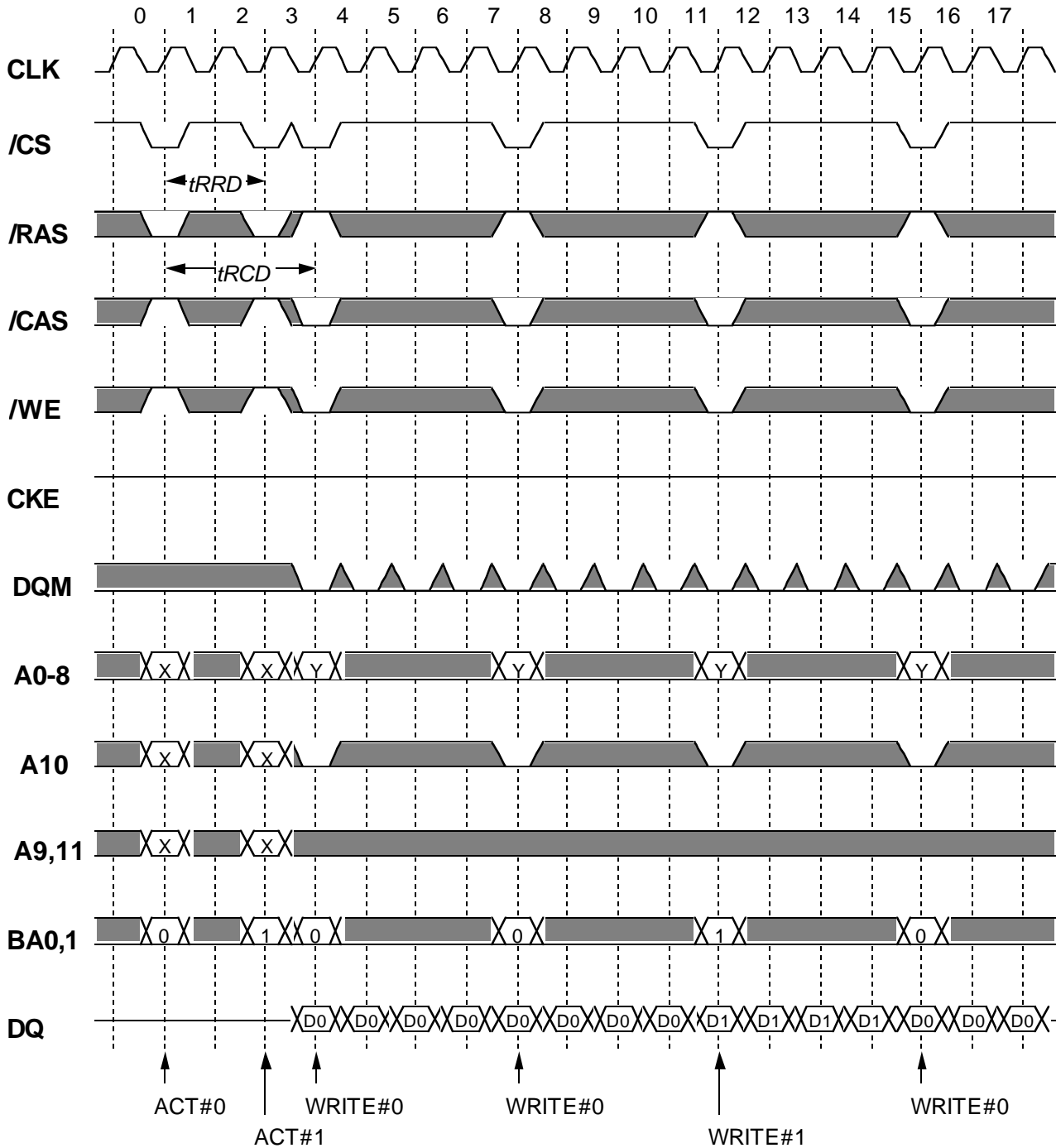## Burst Write (multi bank) with Auto-Precharge @BL=4

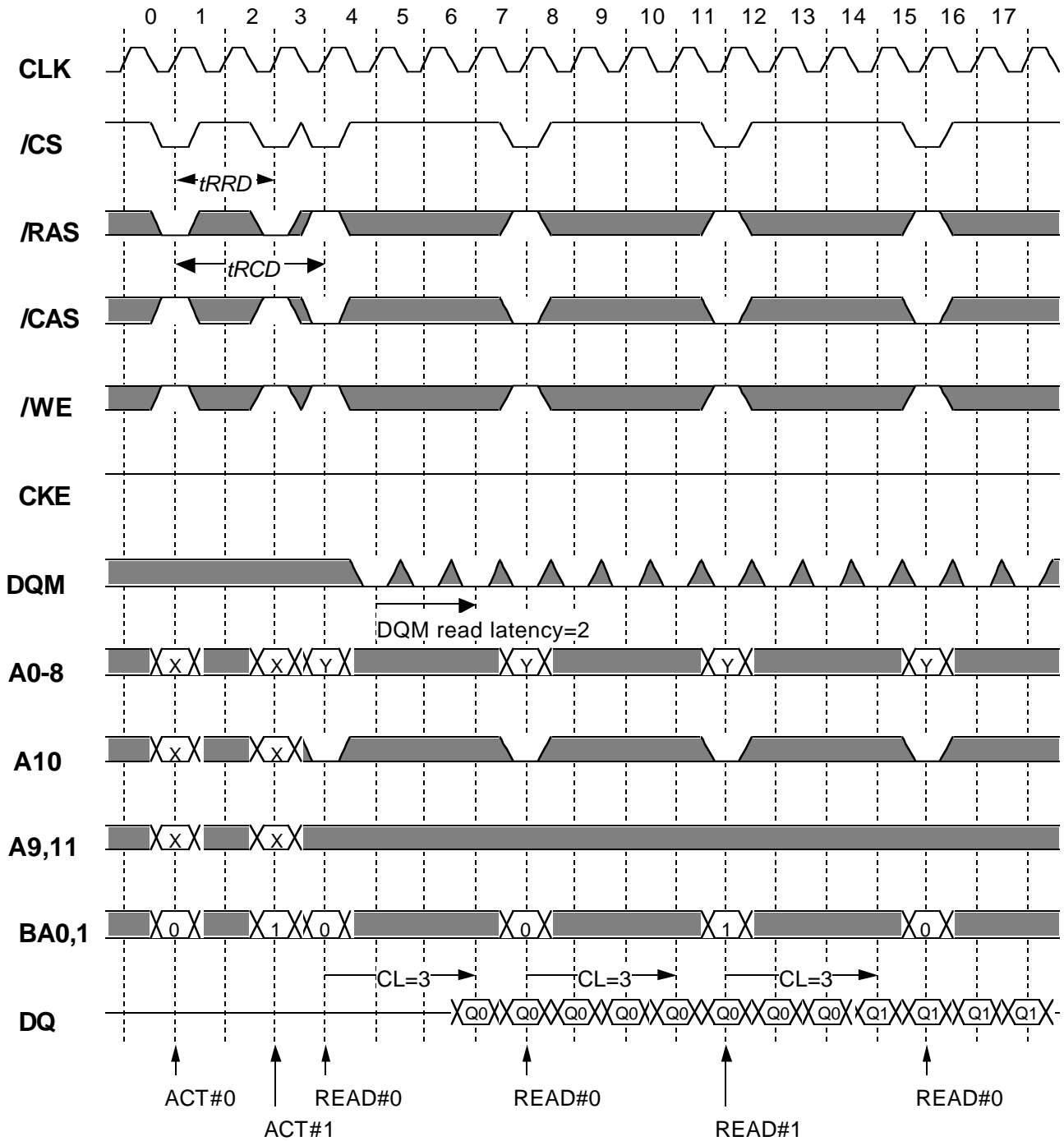*Italic parameter* indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Burst Read (multiple bank) with Auto-Precharge @BL=4 CL=3

CLK
/CS
/RAS
/CAS
/WE
CKE
DQM
A0-8
A10
A9,11
BA0,1
DQ

tRC

$tRRD$ $tRRD$

$tRCD$ $tRCD$ $tRCD$

BL+tRP

BL+tRP

DQM read latency =2

CL=3   CL=3   CL=3

ACT#0
ACT#1
READ#0 with
Auto-Precharge
READ#1 with
Auto-Precharge
ACT#0
READ#0
ACT#1

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
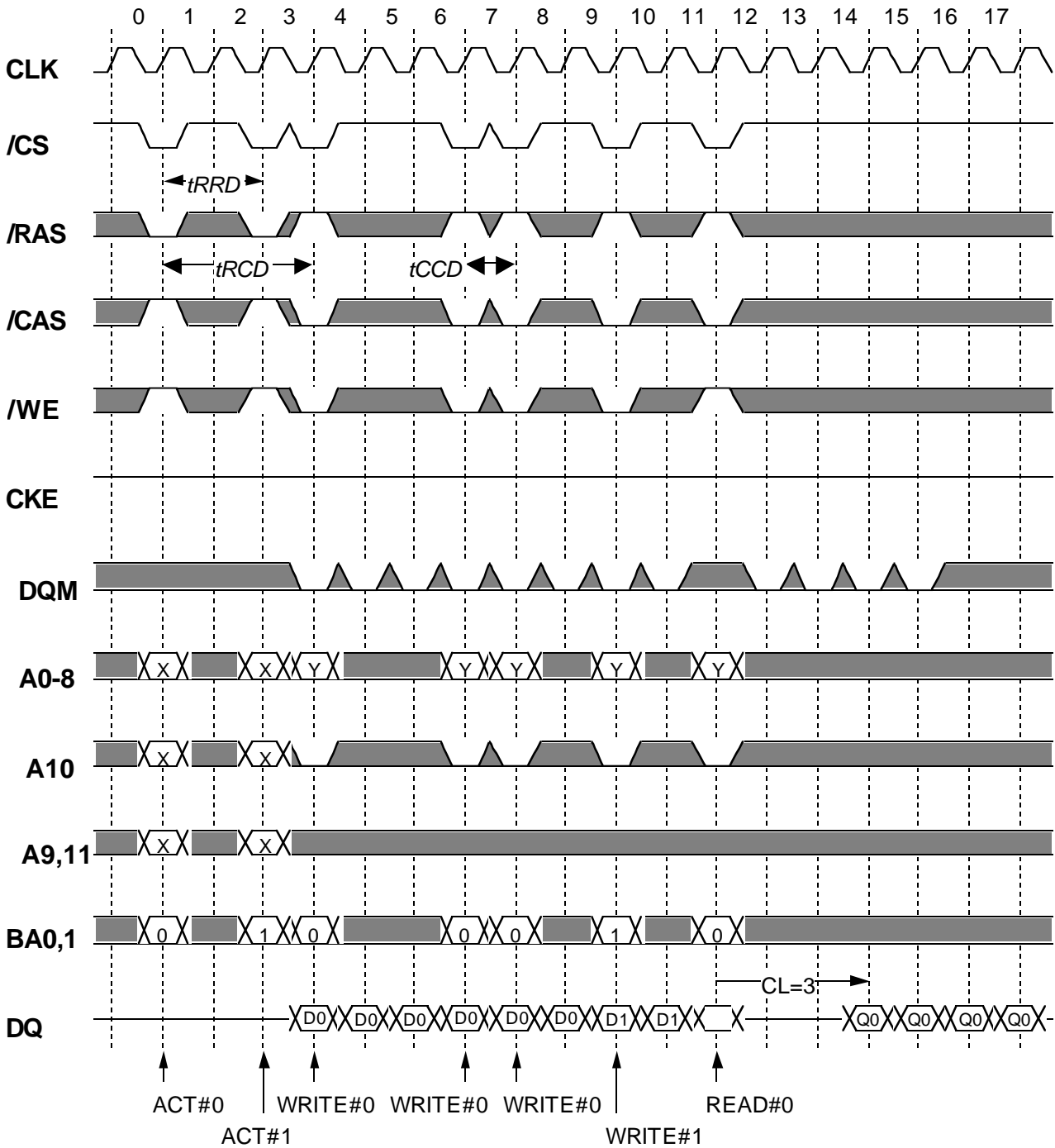
Page Mode Burst Write (multi bank) @BL=4

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Page Mode Burst Read (multi bank) @BL=4 CL=3

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Write Interrupted by Write / Read @BL=4

0 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17

CLK

/CS

tRRD

/RAS

tRCD   tCCD

/CAS

/WE

CKE

DQM

A0-8   X X   X X X Y   Y X Y   X Y   X Y

A10   X X   X X

A9,11   X X   X X

BA0,1   0   1 0   0 X 0   1   0

DQ   D0 X D0 X D0 X D0 X D0 X D0 X D1 X D1   X   Q0 X Q0 X Q0 X Q0

CL=3

ACT#0   WRITE#0   WRITE#0   WRITE#0   READ#0

ACT#1   WRITE#1

Burst Write can be interrupted by Write or Read of any active bank.

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Read Interrupted by Read / Write @BL=4 CL=3
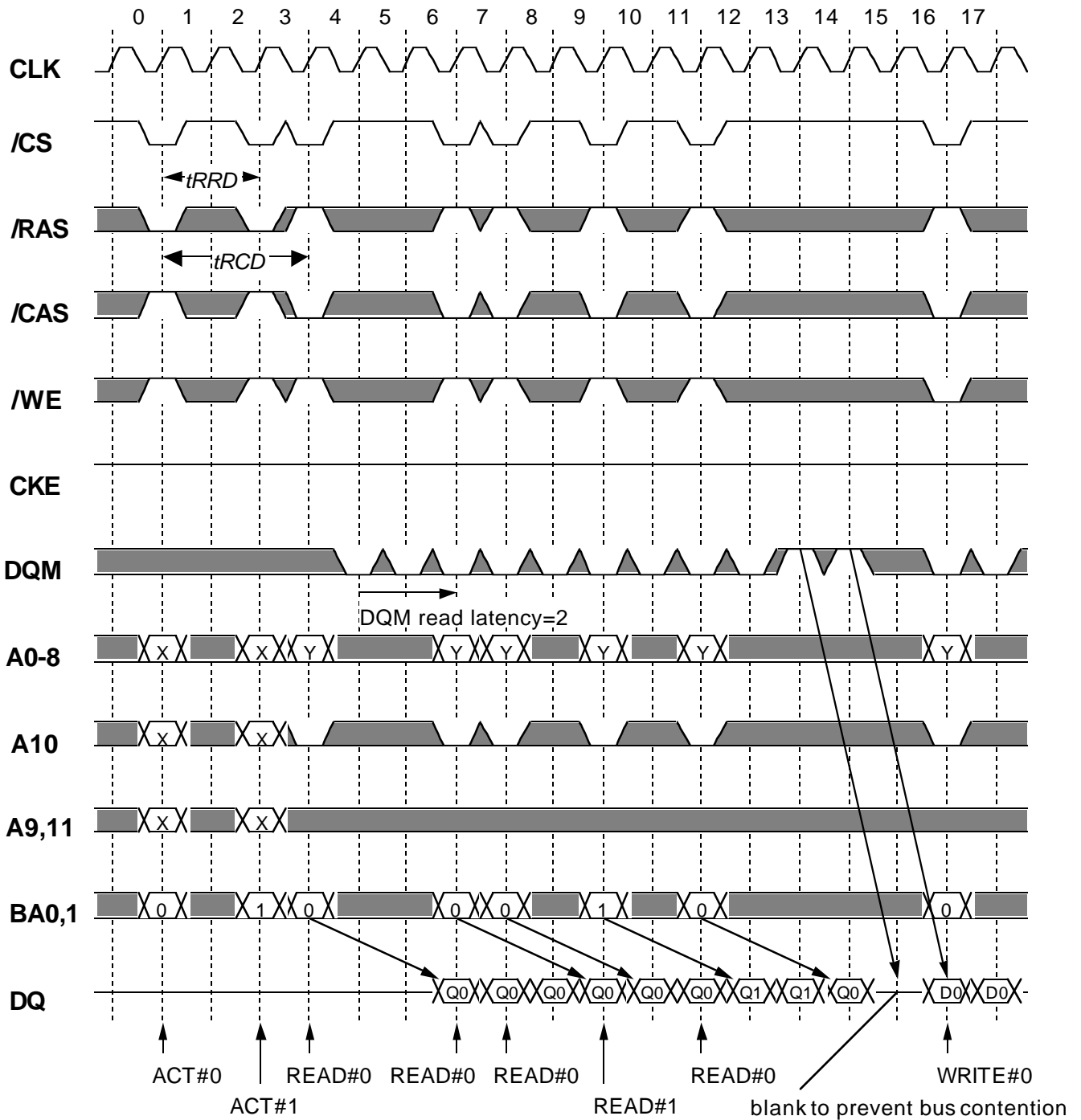
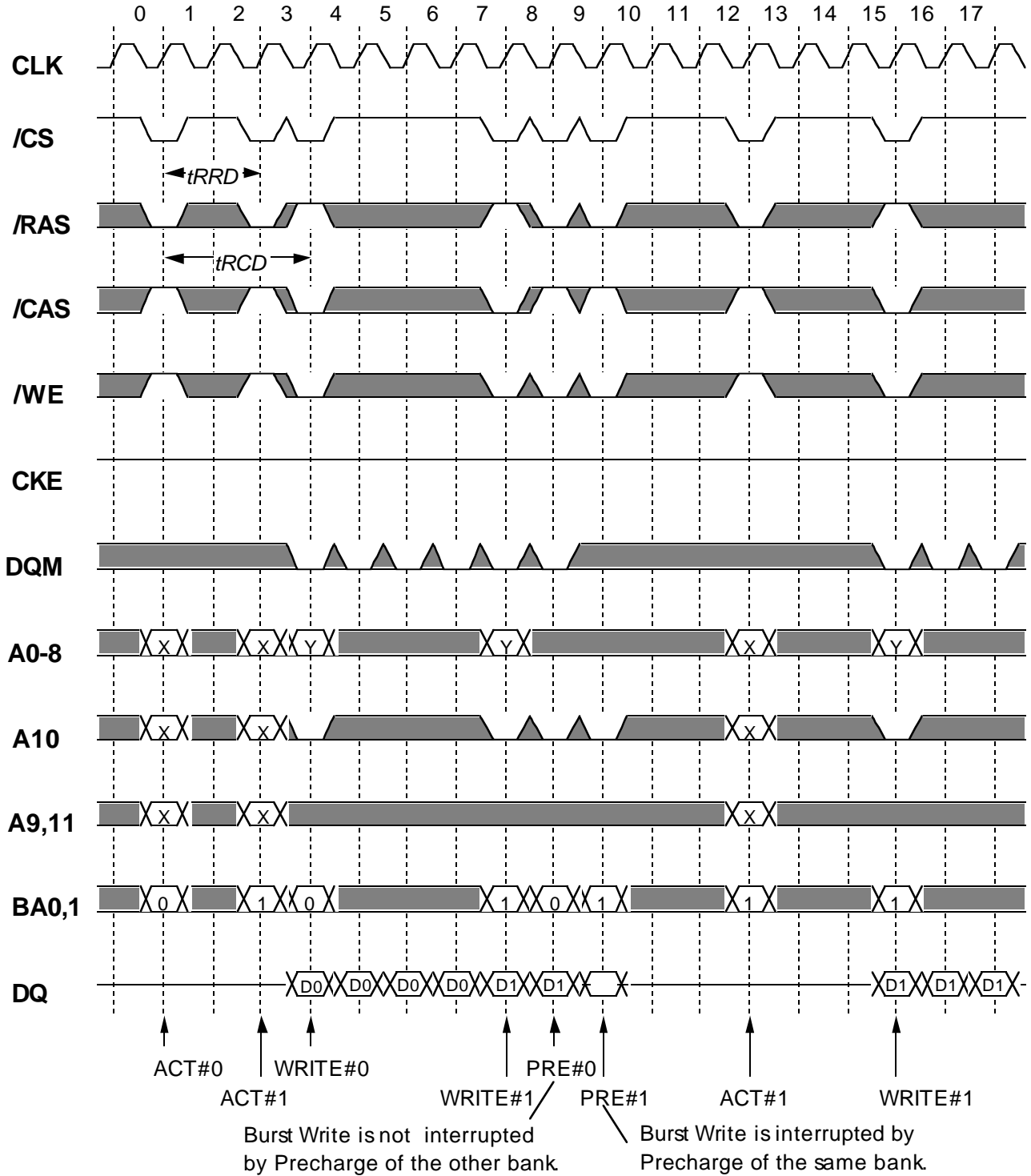Burst Read can be interrupted by Read or Write of any active bank.

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
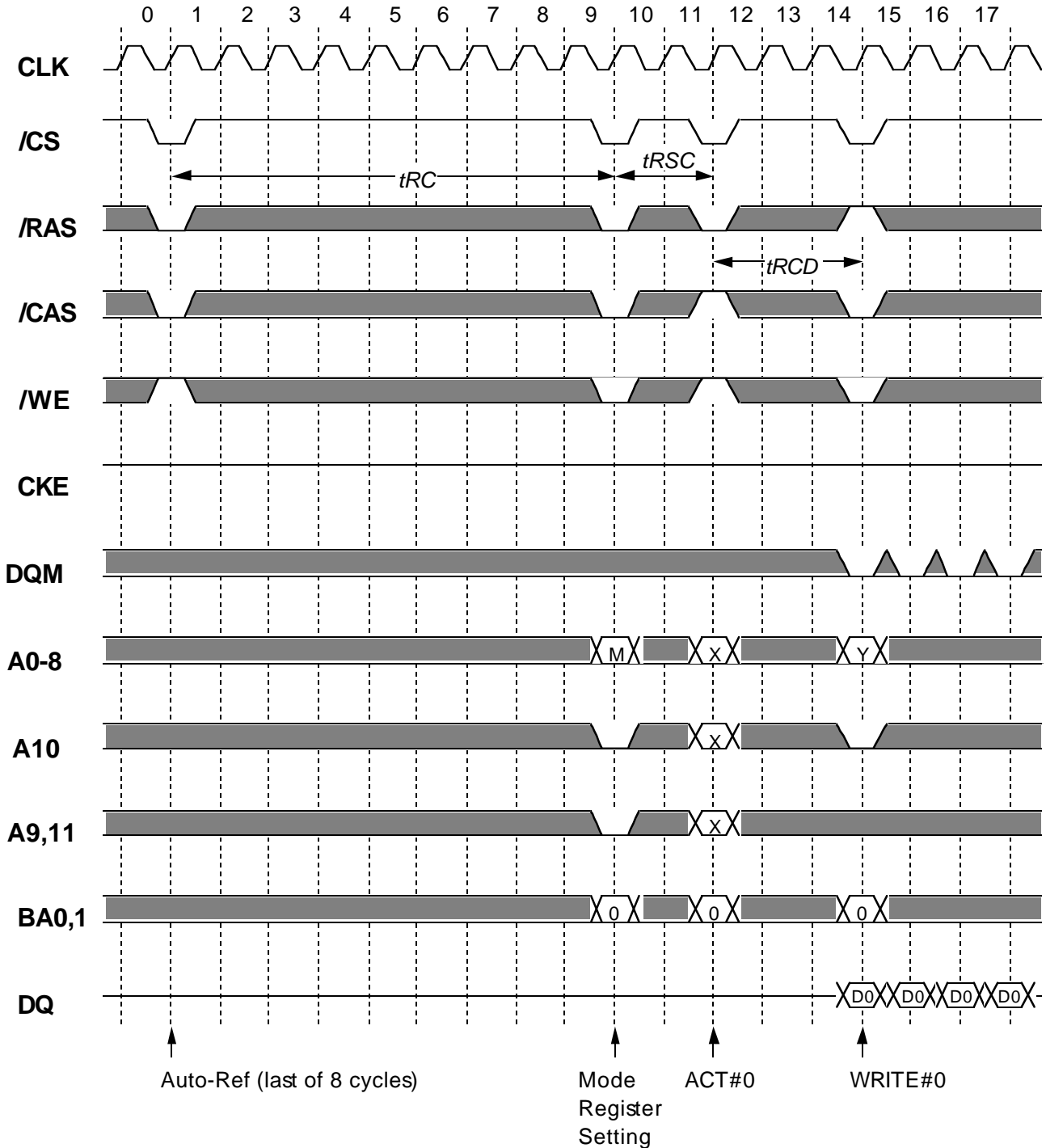
Write Interrupted by Precharge @BL=4

ACT#0

ACT#1

WRITE#0

WRITE#1

PRE#0

PRE#1

ACT#1

WRITE#1

Burst Write is not interrupted
by Precharge of the other bank.

Burst Write is interrupted by
Precharge of the same bank.

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Read Interrupted by Precharge @BL=4 CL=3

ACT#0

ACT#1

READ#0

READ#1

PRE#0

PRE#1

ACT#1

READ#1

Burst Read is not interrupted
by Precharge of the other bank.

Burst Read is interrupted
by Precharge of the same bank.

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
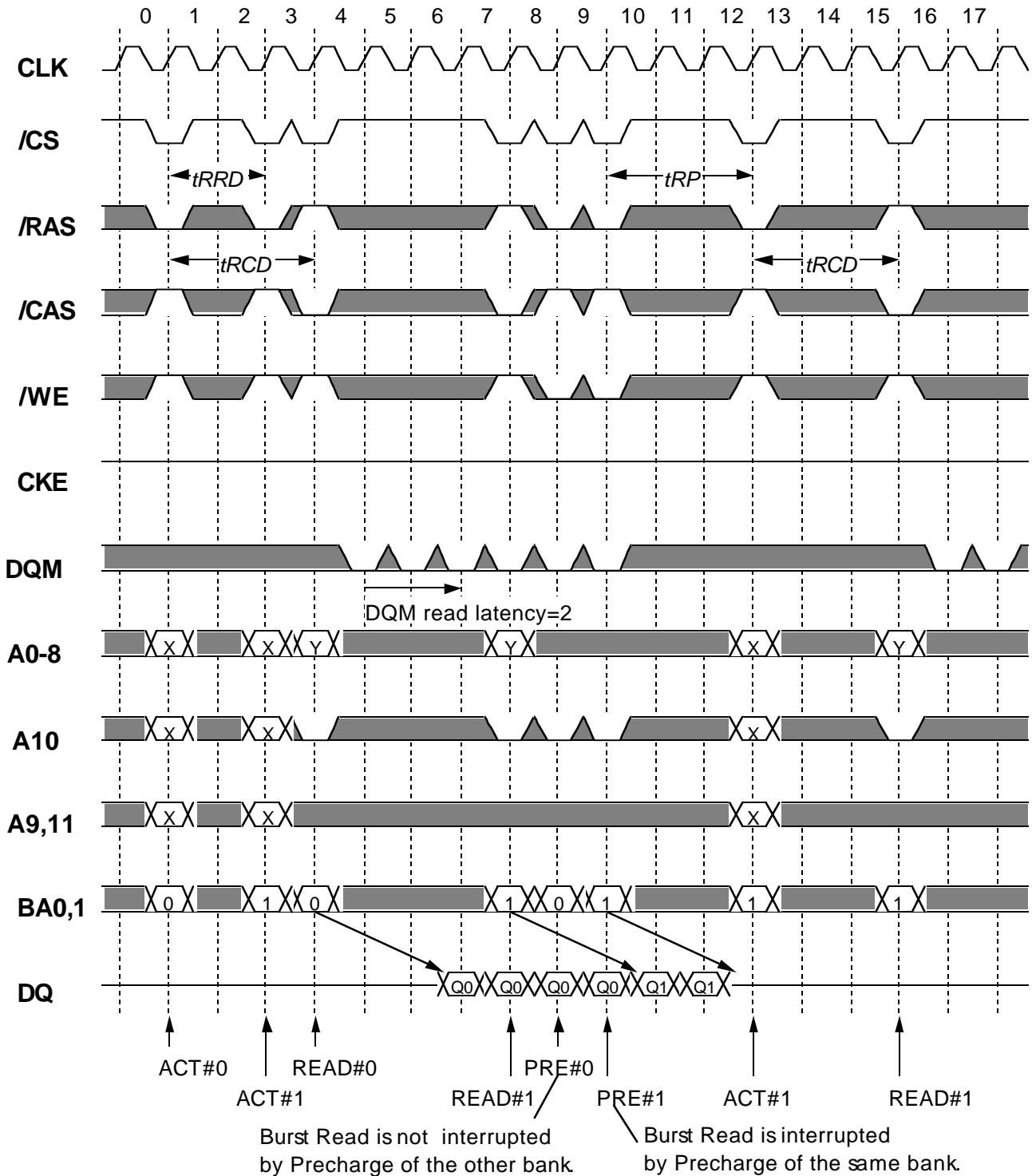
MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Mode Register Setting

Auto-Ref (last of 8 cycles)

Mode Register Setting

ACT#0

WRITE#0

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Auto-Refresh @BL=4

Auto-Refresh

Before Auto-Refresh,
all banks must be idle state.

ACT#0

After tRC from Auto-Refresh,
all banks are idle state.

WRITE#0

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs
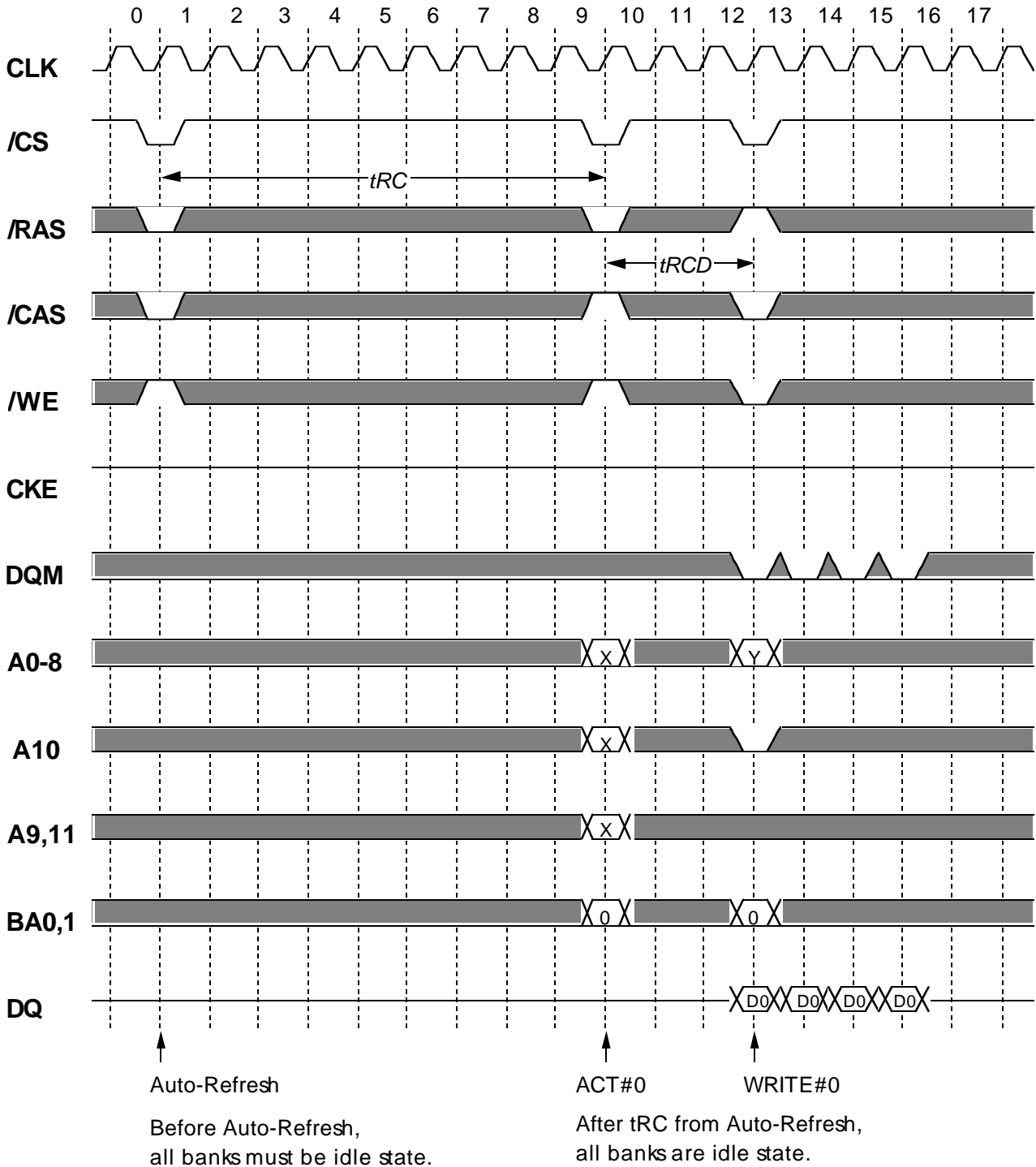
MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Self-Refresh
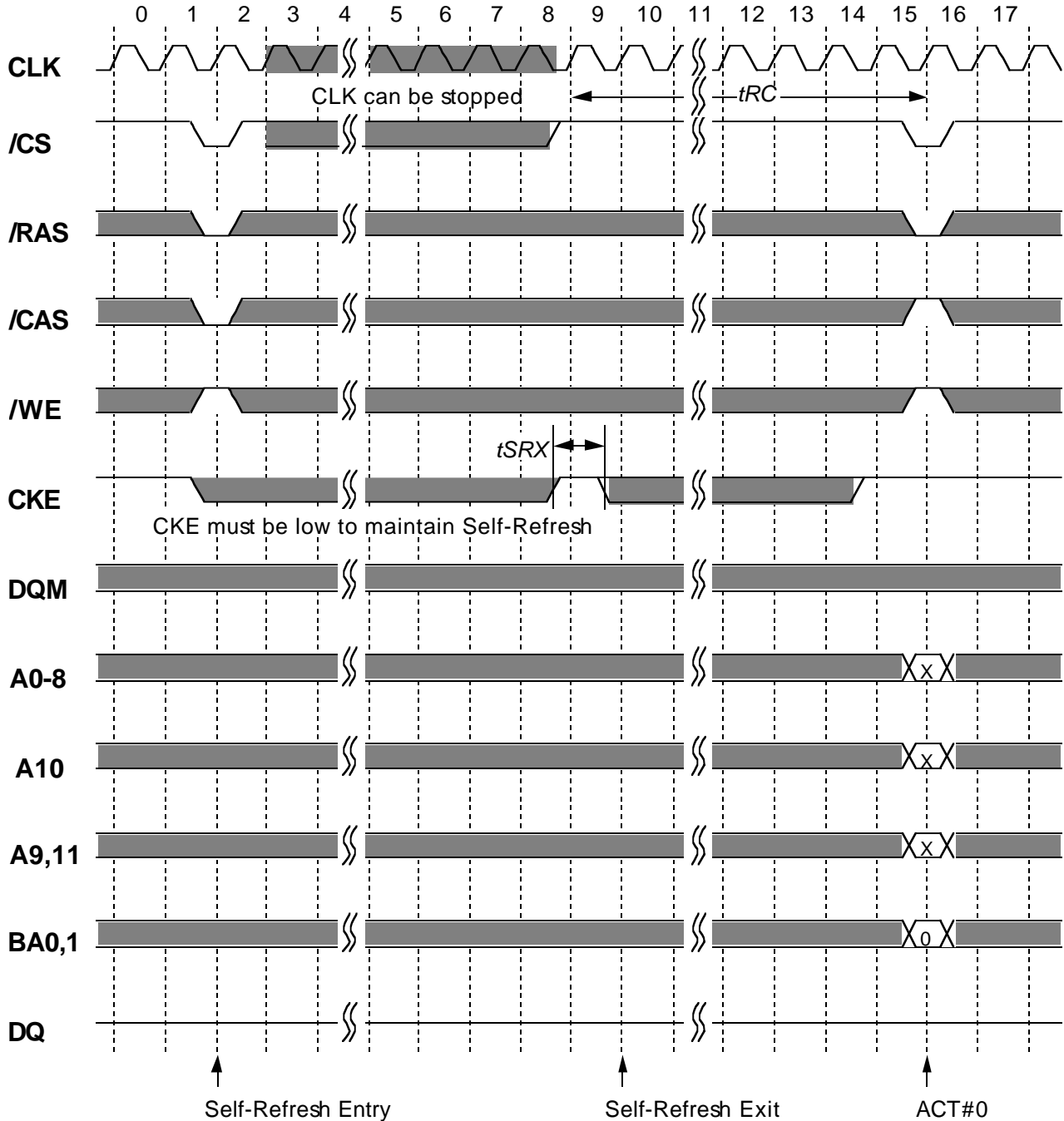
Self-Refresh Entry

Before Self-Refresh Entry,
all banks must be idle state.

Self-Refresh Exit

After tRC from Self-Refresh Exit,
all banks are idle state.

ACT#0

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

DQM Write Mask @BL=4
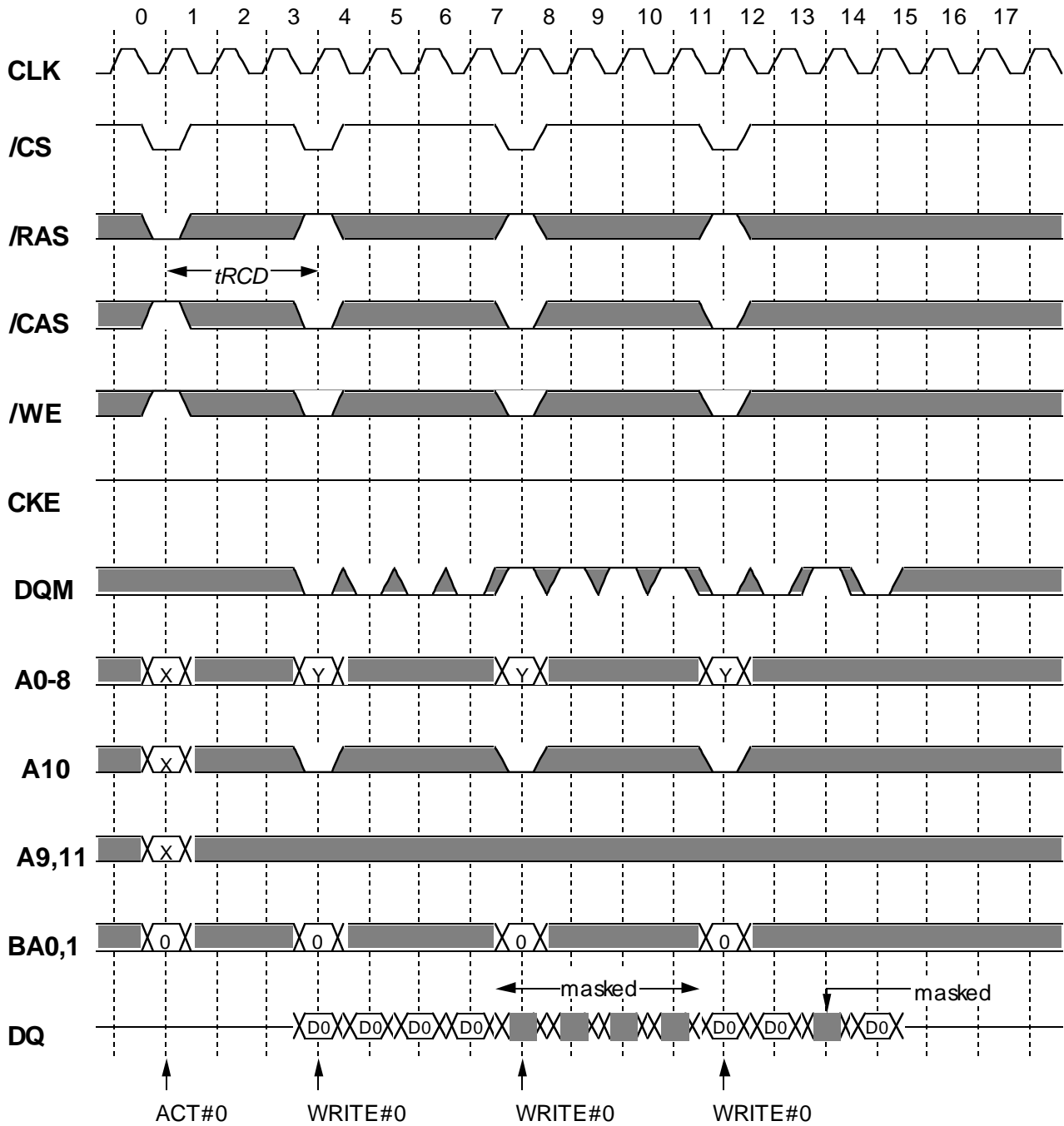
Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
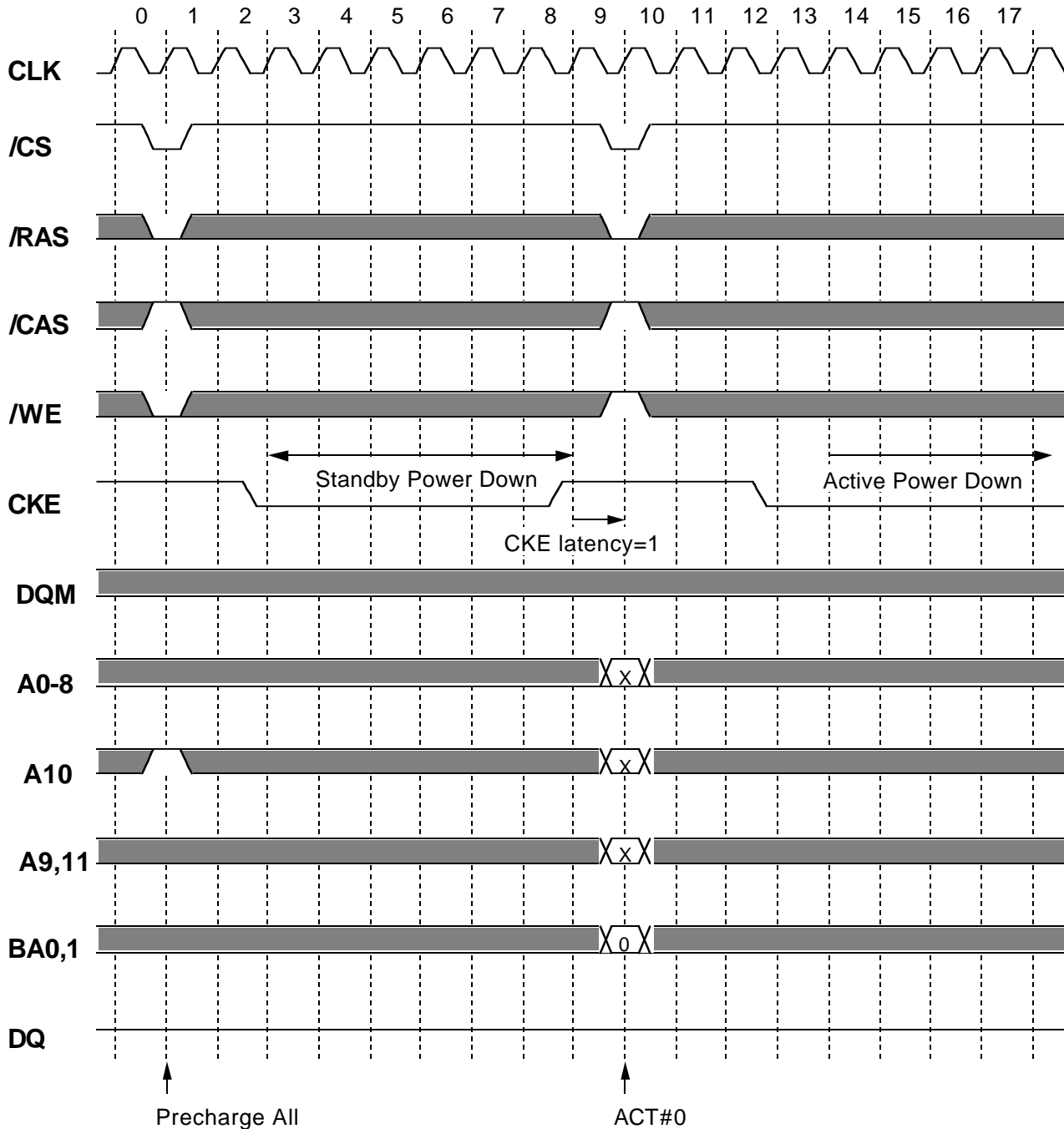
DQM Read Mask @BL=4 CL=3
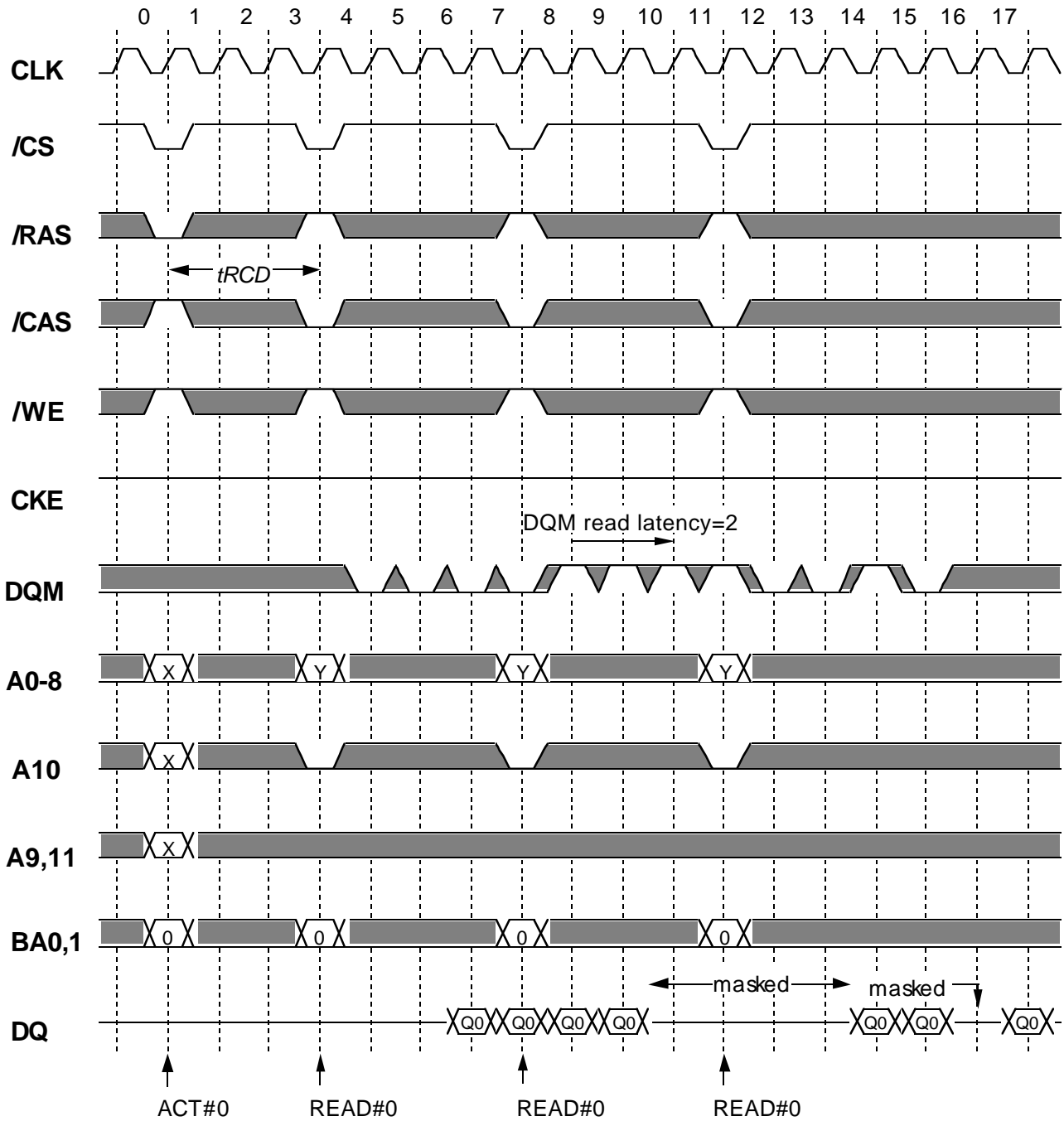
Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8
1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

Power Down

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

CLK Suspend @BL=4 CL=3
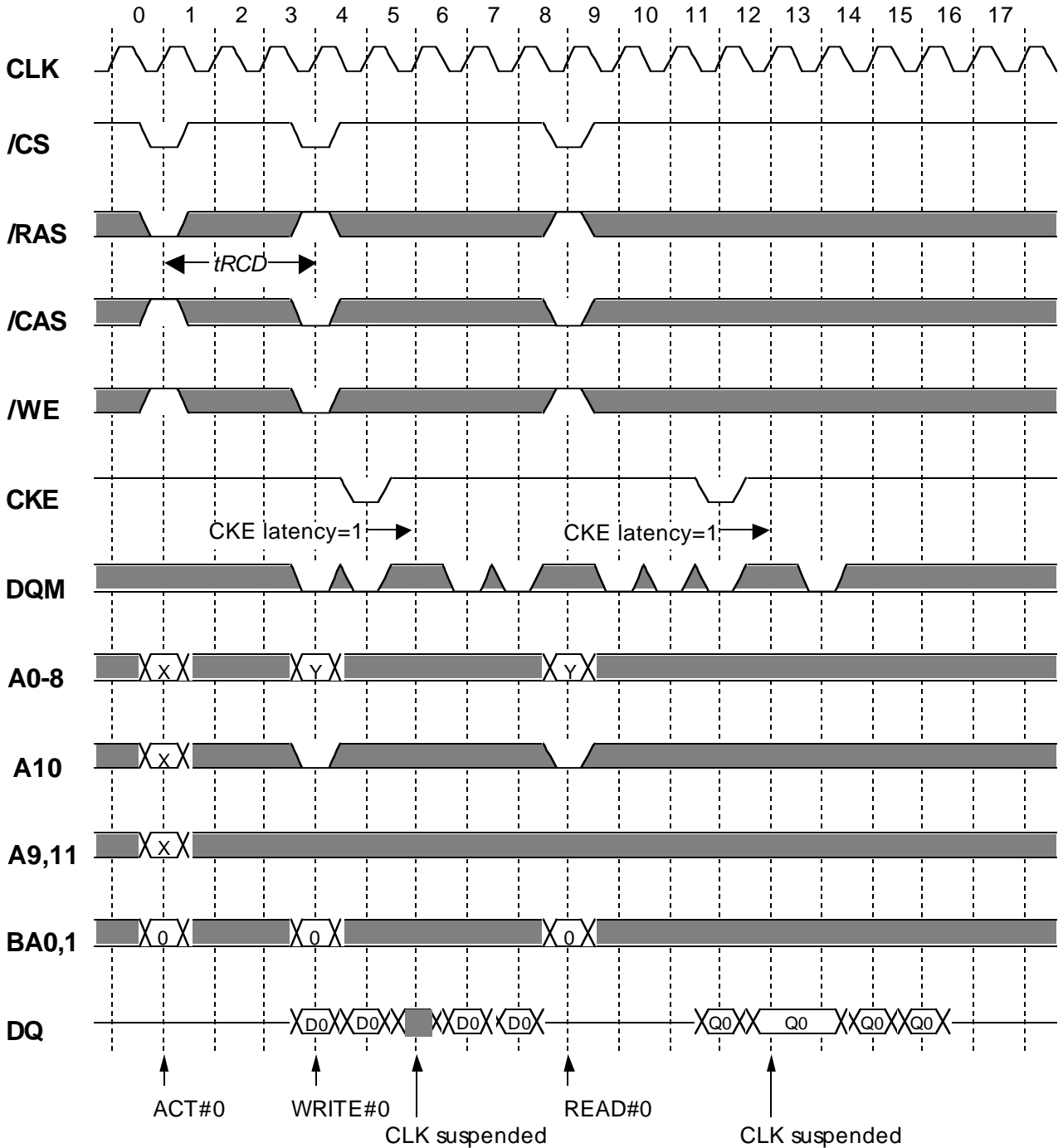
| 0 | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 | 15 | 16 | 17 |

CLK

/CS

/RAS

$tRCD$

/CAS

/WE

CKE

CKE latency=1   CKE latency=1

DQM

A0-8   X   Y   Y

A10   X

A9,11   X

BA0,1   0   0   0

DQ   D0 D0   D0 D0   Q0 Q0 Q0 Q0

ACT#0   WRITE#0   CLK suspended   READ#0   CLK suspended

Italic parameter indicates minimum case

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM

OUTLINE

Preliminary Spec.
Some contents are subject to change without notice.

MITSUBISHI LSIs

MH16S72APHB -6,-7,-8

1,207,959,552-BIT (16,777,216 - WORD BY 72-BIT)Synchronous DRAM
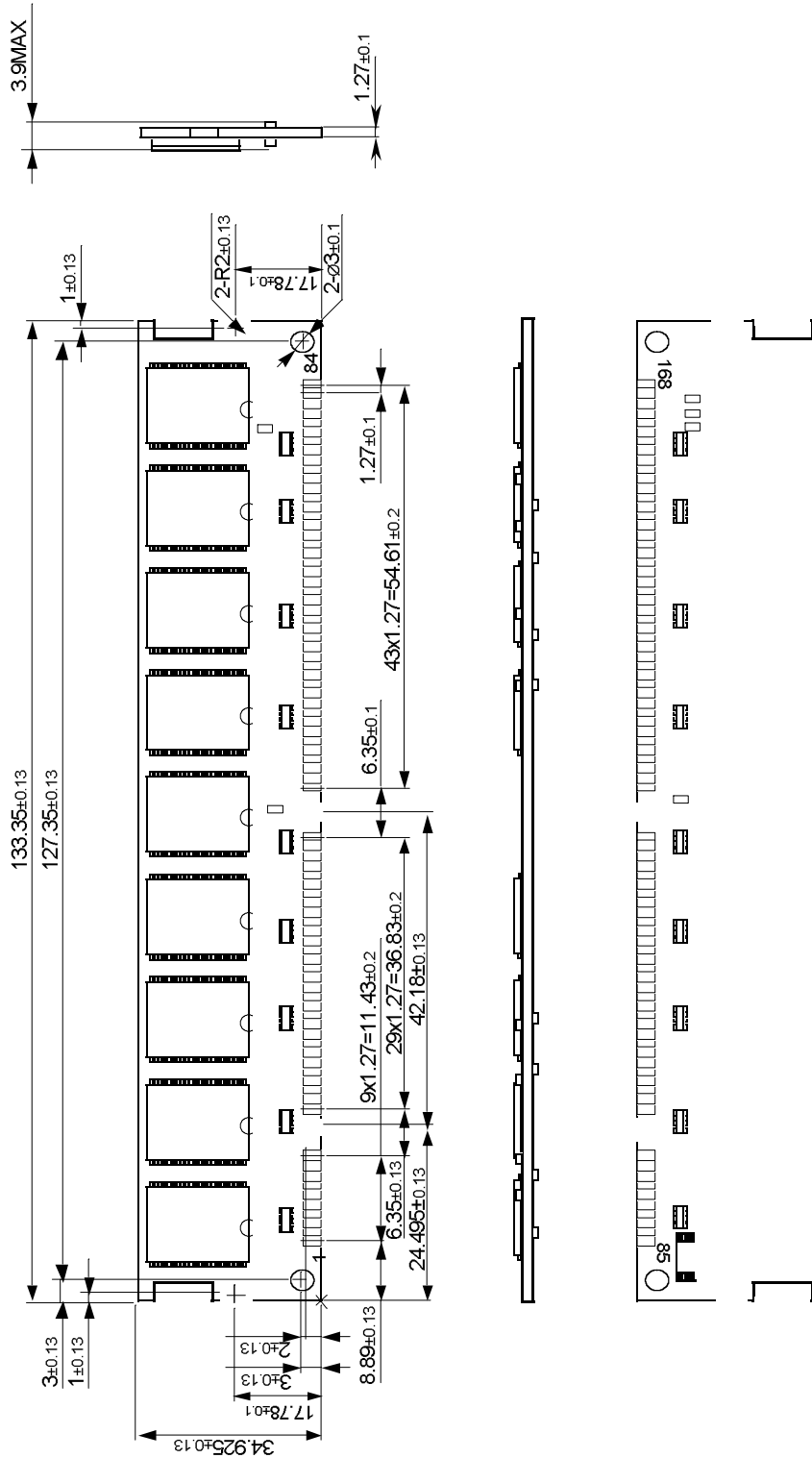
Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.

2. Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein. The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Semiconductor home page (http://www.mitsubishichips.com).

4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products.
Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

5. Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.

6. The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.

7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

8. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.